



Single Event Transients RHA Policy - Agencies

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Radiation Hardness Assurance

- Define radiation environment
 - Heavy ions (GCR, solar ions)
 - Protons (trapped, solar)
- Bound the part response
 - SET testing
- Define system /subsystem response to the radiation environment
 - SET criticality analysis
 - SET rate prediction

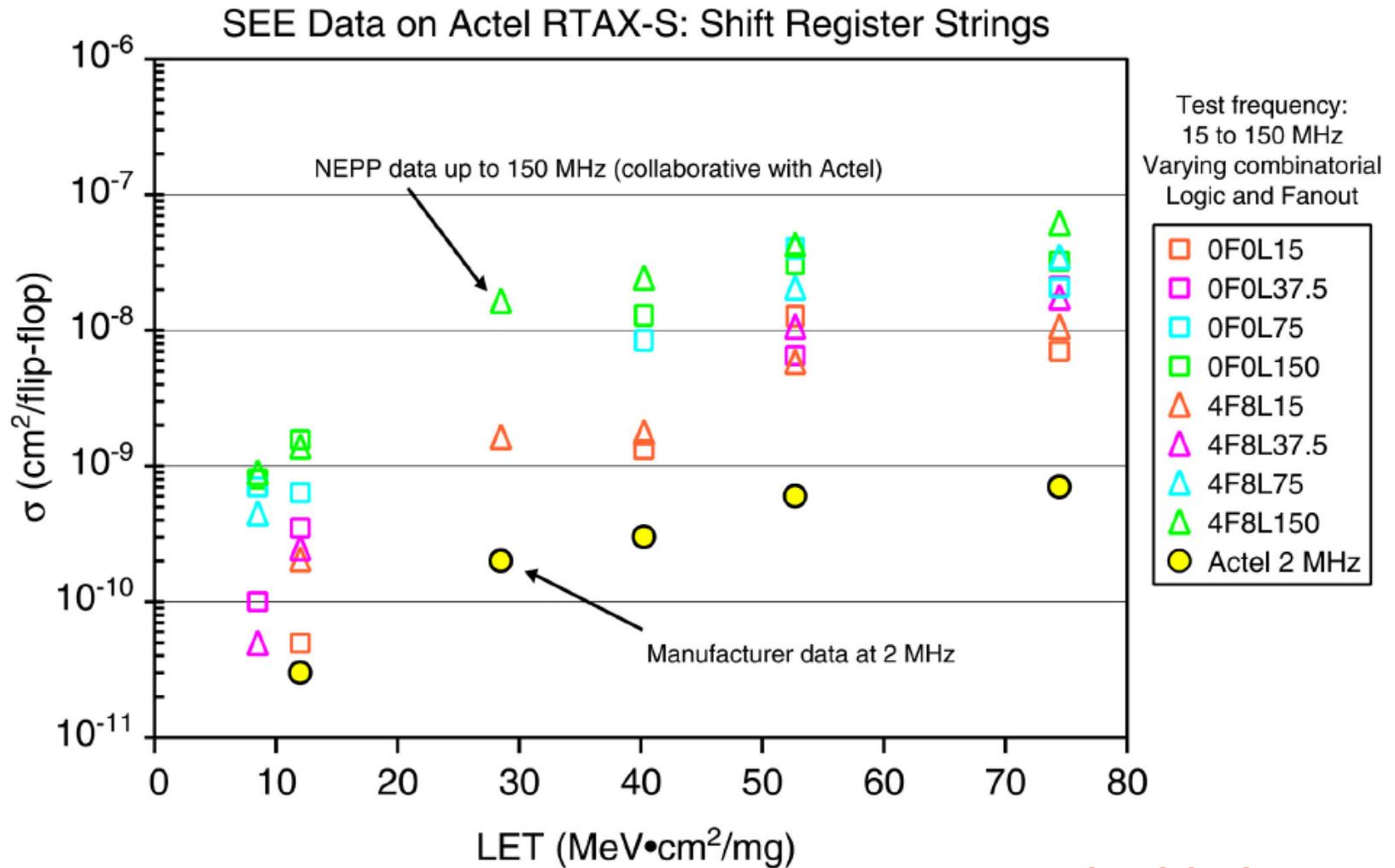
Available Documents

- Draft ECSS-Q-ST-60-15C
 - Space Product Assurance
 - Radiation Hardness Assurance
- ESCC25100 issue 1, October 2002
 - Single Event Effect Test Method and Guidelines

Bound the Part Response

- Draft ECSS-Q-ST-60-15C
 - Section 5.3 SEE hardness assurance
 - Requirement a: No SEE shall cause damage to a system or a subsystem or induce performance anomalies or outages
 - Requirement b: **Each active electronic part shall be assessed for sensitivity to SEE effects.**
 - Requirement c: **If component test data does not exist, heavy ion ground testing shall be required.**
- ESCC25100 issue 1, October 2002
 - Section 4.2.1 Single Event Upset
 - “Analogue and mixed analogue/digital technologies may generate false outputs or transients as the result of SEE. The test system shall be capable of monitoring and logging these effects.”

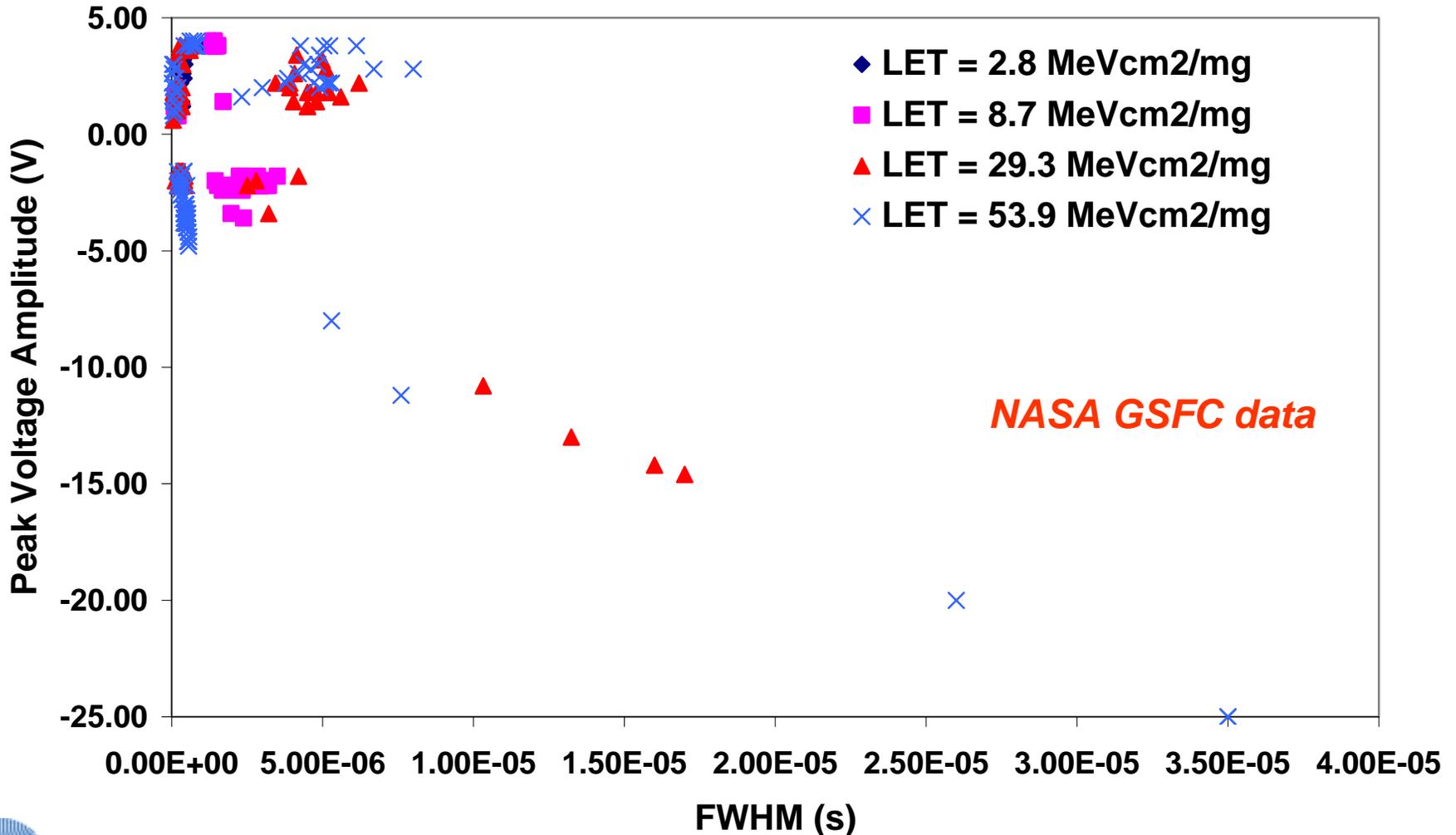
Bound the Part Response, Digital IC



NASA GSFC data

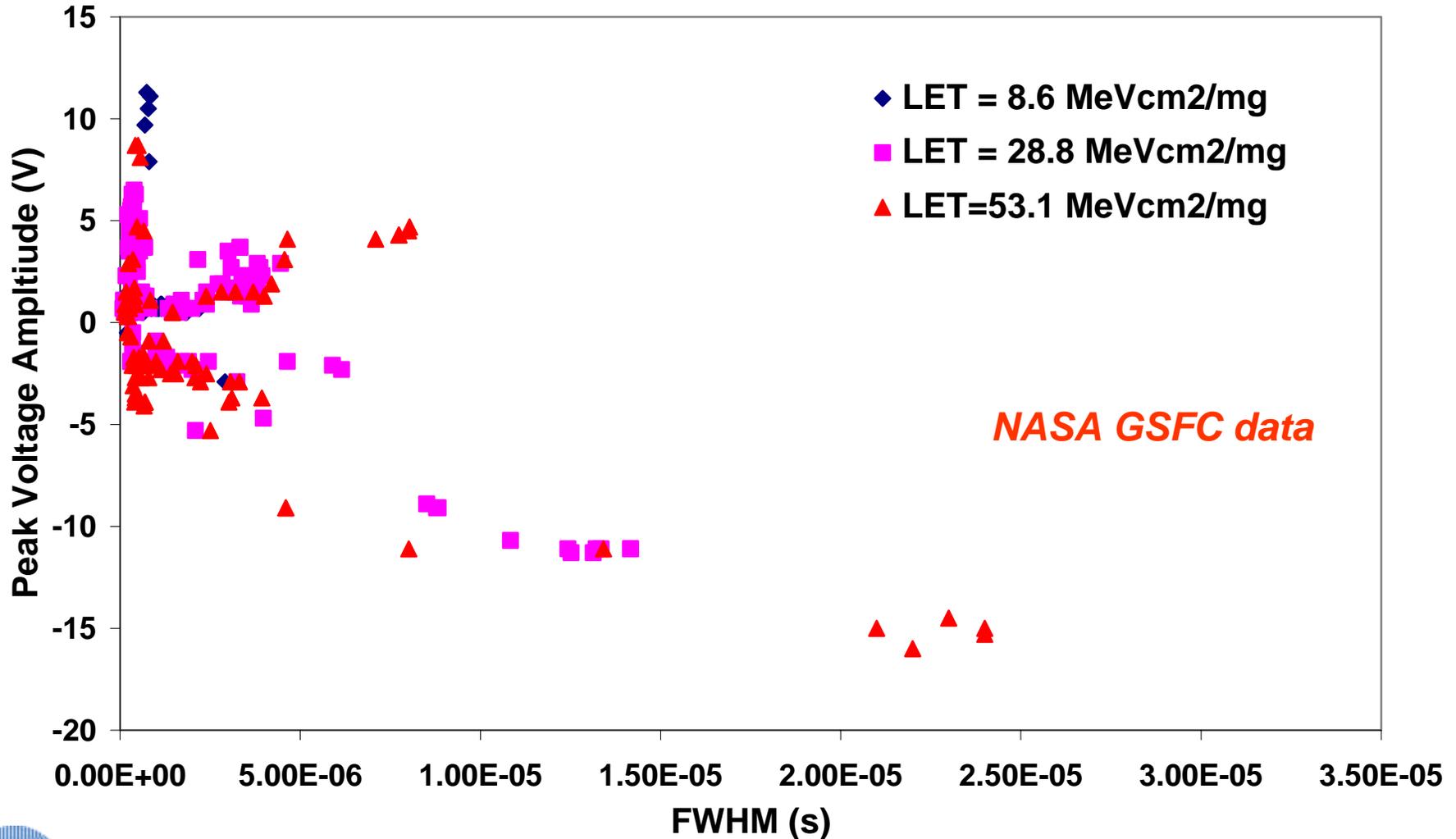
Bound the Part Response, Analog IC

LM124, Voltage Follower $V_{in} = 10V$



Bound the part response, Analog IC

LM124, Voltage Follower $V_{in}=1V$



Bound the part response

- Draft ECSS-Q-ST-60-15C
 - Section 5.3 SEE hardness assurance
 - Requirement e: All SEE testing shall be performed according to ESCC25100. Testing conditions shall be representative of application conditions. This shall include, but is not limited to: **bias conditions, clock frequency**.....

Bound the Part Response Worst Case Models for analog ICs

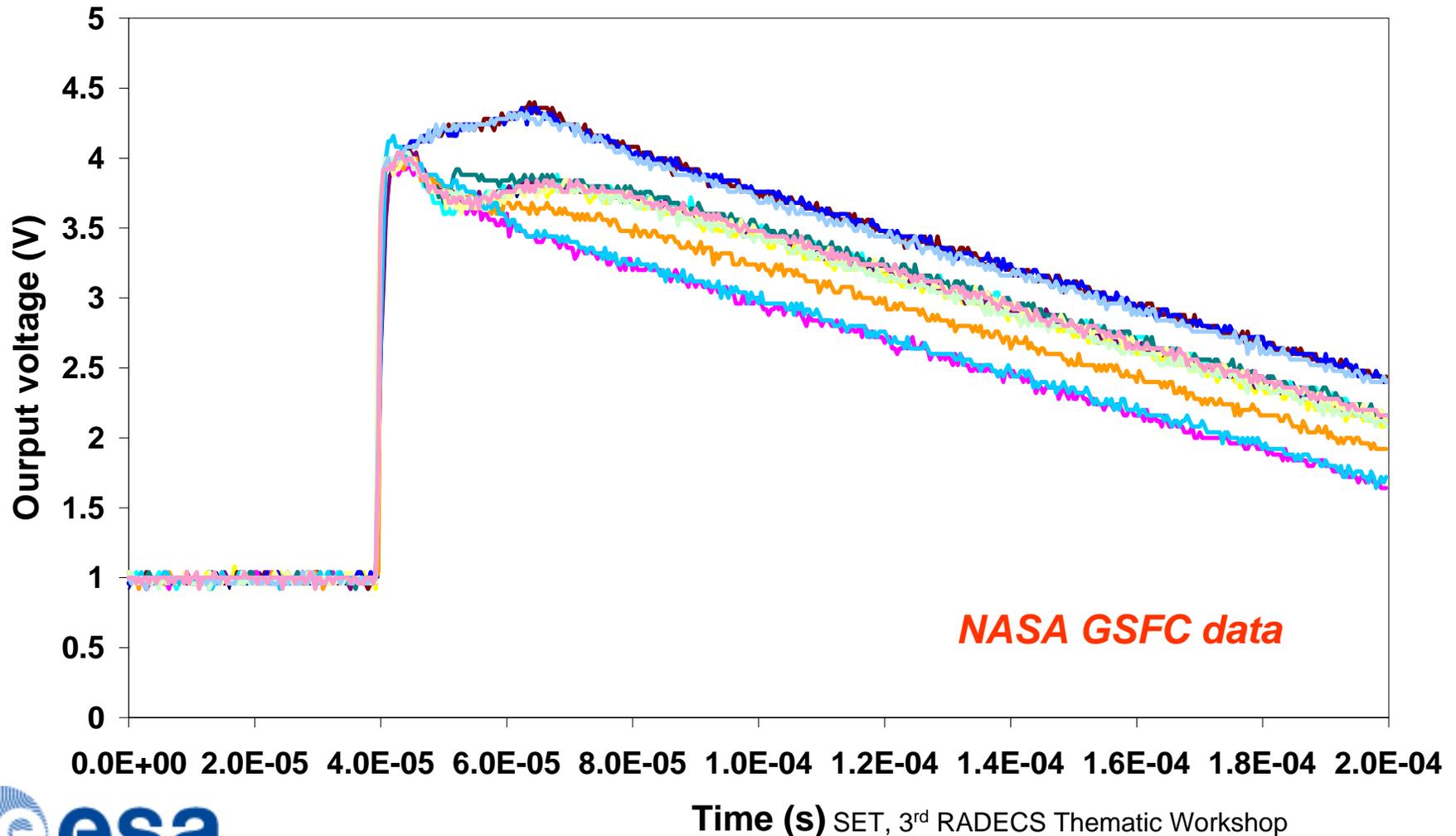
Operational amplifiers	$\Delta V_{\max} = + / - V_{cc} \ \& \ \Delta t_{\max} = 40 \ \mu s$
Voltage Comparators	$\Delta V_{\max} = +/- V_{cc} \ \& \ \Delta t_{\max} = 10 \ \mu s$
Voltage Regulators	$\Delta V_{\max} = +/- V_{cc} \ \& \ \Delta t_{\max} = 10 \ \mu s$
Voltage References	$\Delta V_{\max} = +/- V_{cc} \ \& \ \Delta t_{\max} = 10 \ \mu s$

From ALPHASAT RHA requirements

Bound the Part Response

Worst case SETs, Example

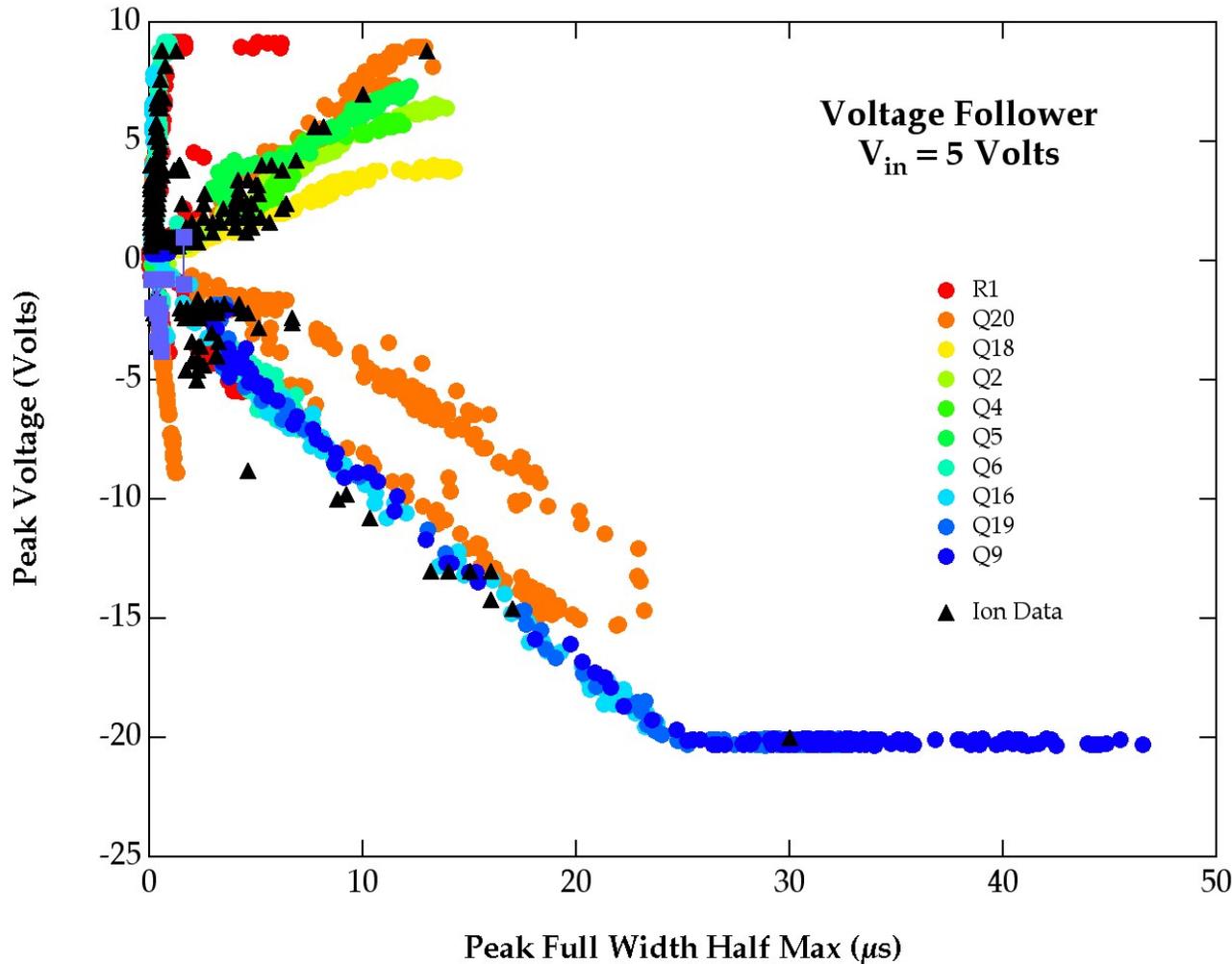
OP 293 long transients



NASA GSFC data



Bound the Part Response Obtain Worst case SET with laser



LM124,
heavy ion
(53 MeVcm²/mg)
and laser data

After Buchner, SEE symposium 2004

SET, 3rd RADECS Thematic Workshop
Villigen, Switzerland

Bound the Part Response

- Draft ECSS-Q-ST-60-15C
 - Section 5.3 SEE hardness assurance
 - Requirement c: If component test data does not exist, heavy ion ground testing shall be required.
 - Note: It is common practice to use a worst case SET model for the SET criticality analysis of analog ICs. This approach is not recommended. However, an approach using worst case SETs obtained from laser testing can be accepted.

Bound the part response

Proton induced SET

- Draft ECSS-Q-ST-60-15C
 - Section 5.3 SEE hardness assurance
 - Requirement i: Parts analysis and possibly proton testing shall take place based on LET threshold (LET_{th}) of the candidate devices. Above a LET_{th} of 75 MeVcm²/mg, the parts can be considered as immune to SEE in space and no further analysis is required. Below this level SEE analysis shall be performed. And, below a LET_{th} of 15 MeVcm²/mg proton induced sensitivity analysis shall be analyzed as well, and **proton test data shall be required**.

SET criticality analysis

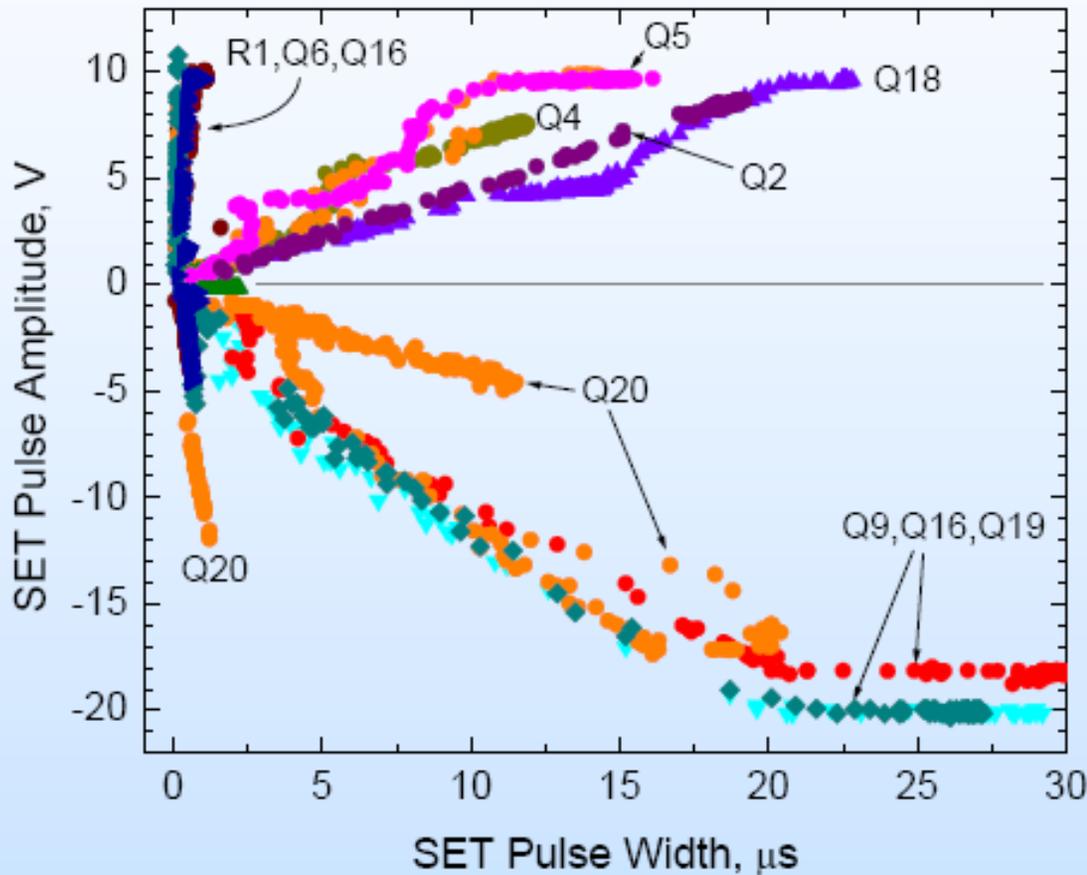
- Draft ECSS-Q-ST-60-15C
 - Section 5.3 SEE hardness assurance
 - Requirement k: for non destructive events like SEU, SET, and MBU, the criticality of a component in its specific application shall be defined including all possible impacts at higher, subsystem and system, levels

SET event rate calculation

- Draft ECSS-Q-ST-60-15C
 - Section 5.3 SEE hardness assurance
 - Requirement I: When a SEE on a given component for a given application is considered critical or potentially critical, the mission event rate shall be calculated according to the methods described in ECSS-E-ST-10-12C. This rate shall be calculated for the mission background environment and a solar event environment as well as defined in mission radiation environment specification. A RDM of 10 shall be applied on event rates.

SET event rate calculation in analog ICs

Number of sensitive nodes/volumes



LM124, laser data

After Buchner, SEE symposium 2004

SET event rate calculation in analog ICs

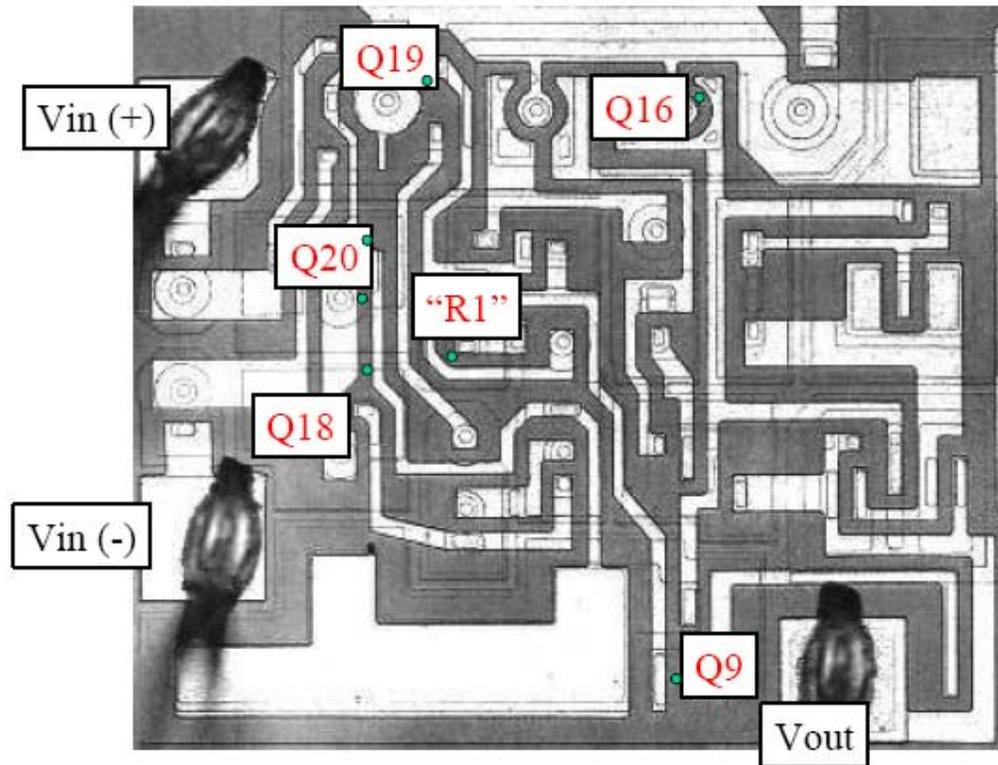
number of sensitive nodes/volumes

- Example: LM139
 - Effect of the number of sensitive nodes

Number of sensitive nodes	Sensitive node area (μm^2)	# GCR induced SET CREME96, solmin (#/comparator-day)	# SPE induced SET CREME96, worst day (#/comparator-day)
1	60000	4.99E-03	1.63E+00
10	6000	4.83E-03	7.84E-01
100	600	4.34E-03	2.17E-01

SET event rate calculation in analog ICs

Thickness of sensitive volume

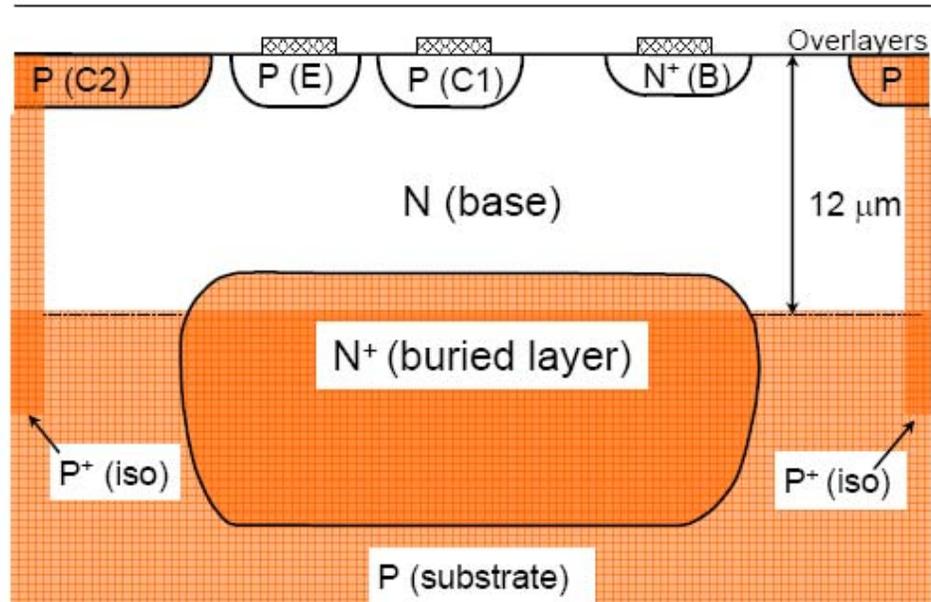
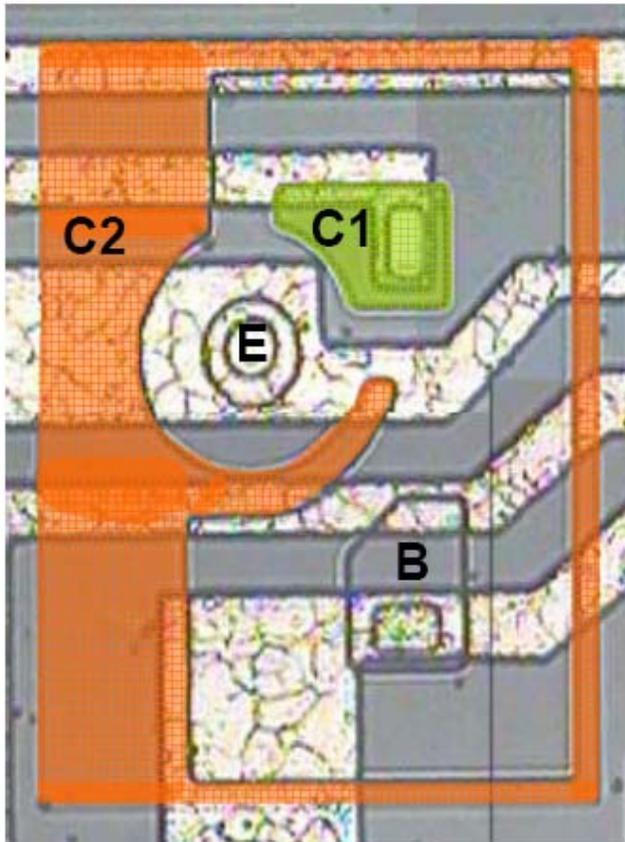


LM124

After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

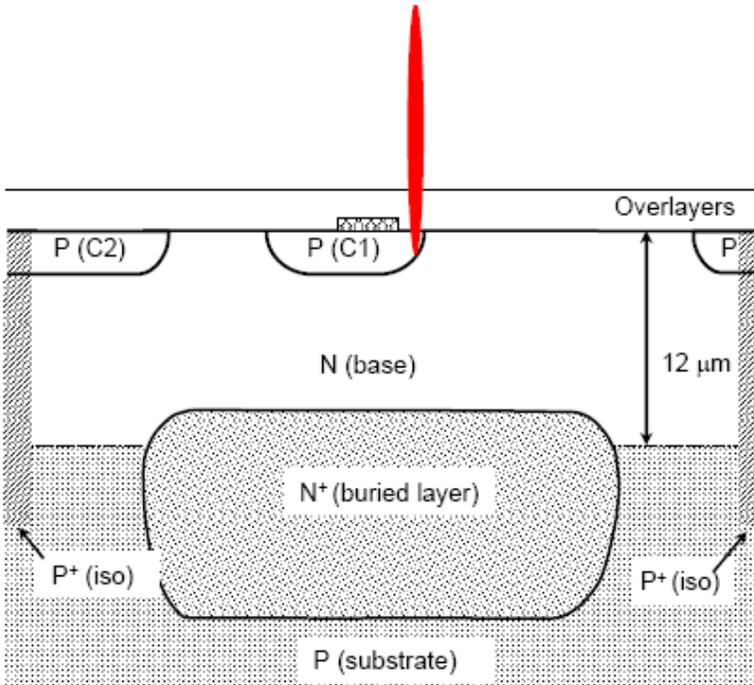
Thickness of sensitive volume



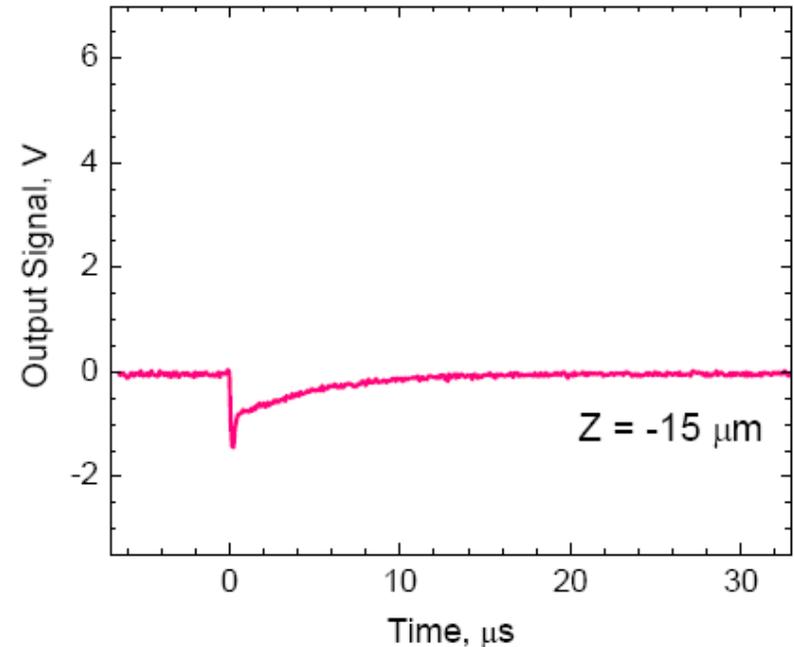
After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume



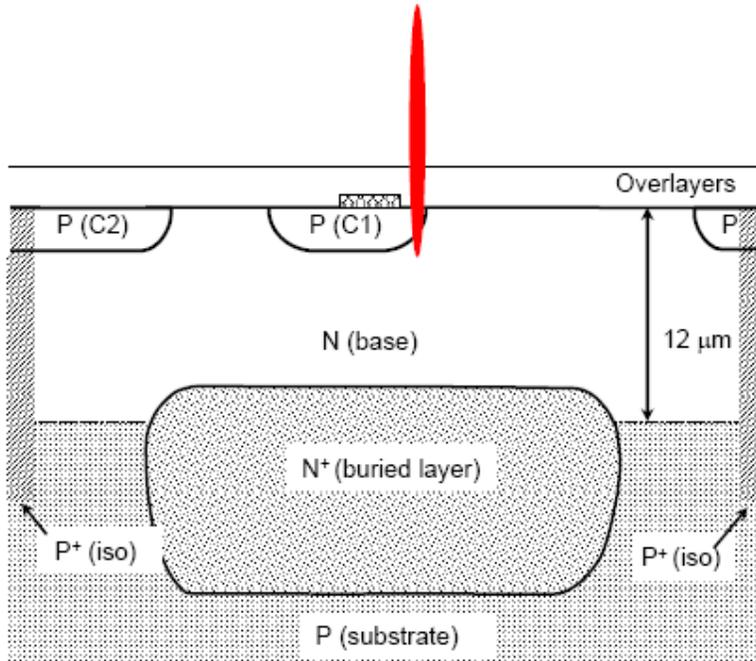
Inverting Configuration, gain of 20



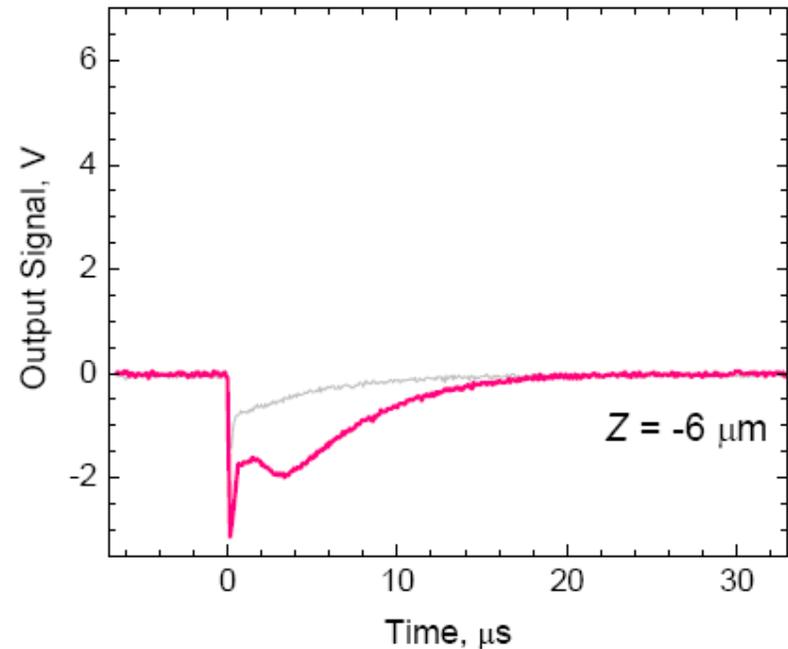
After McMorrow, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume



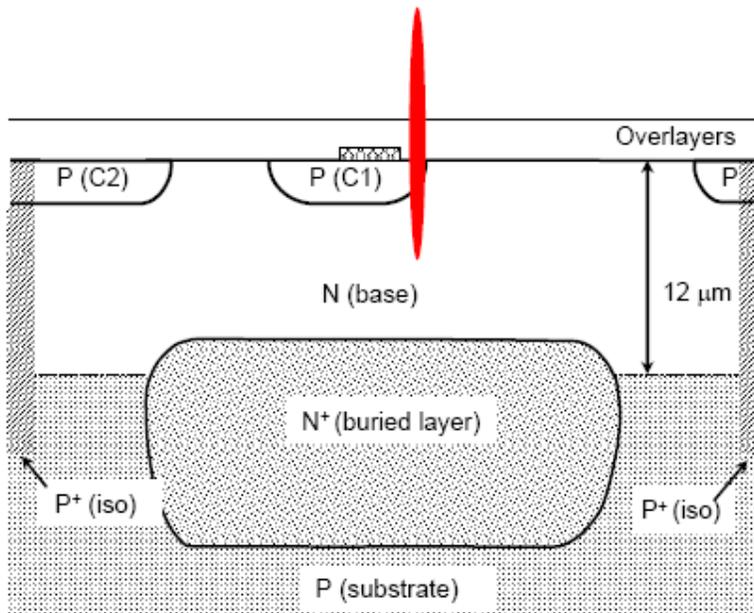
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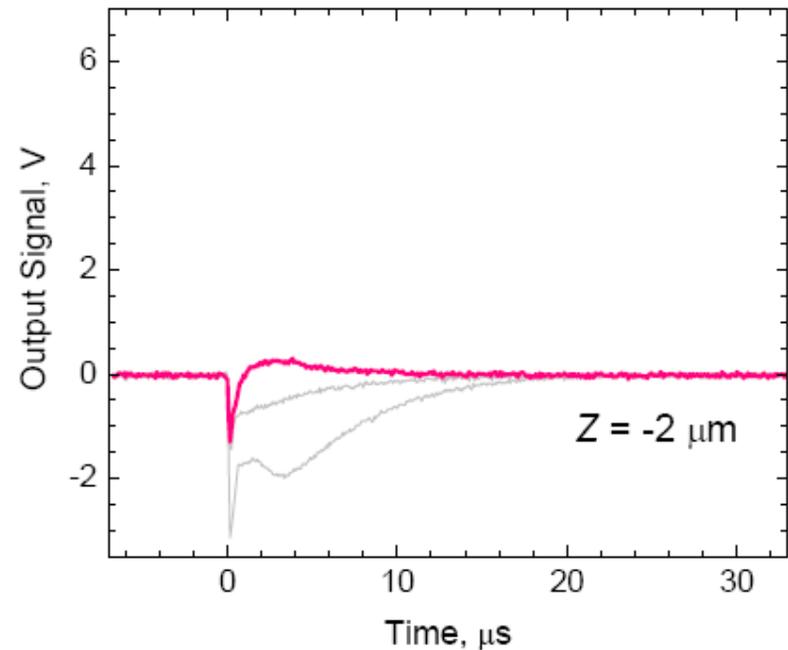
After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume



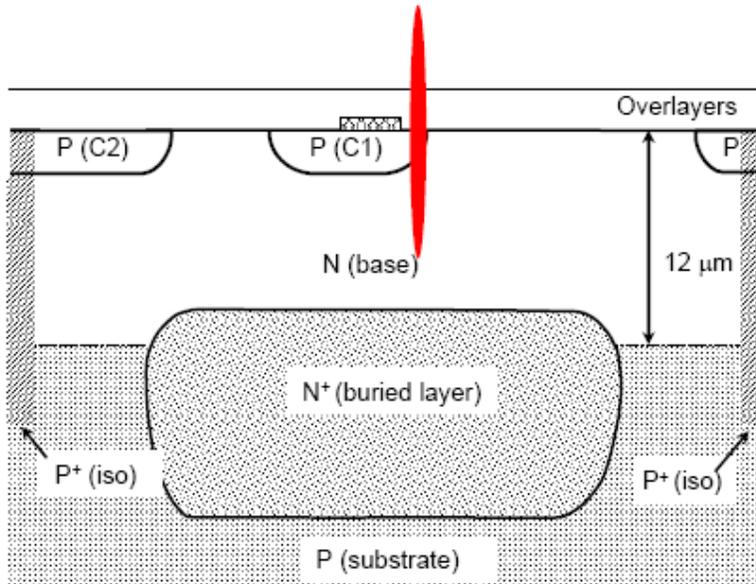
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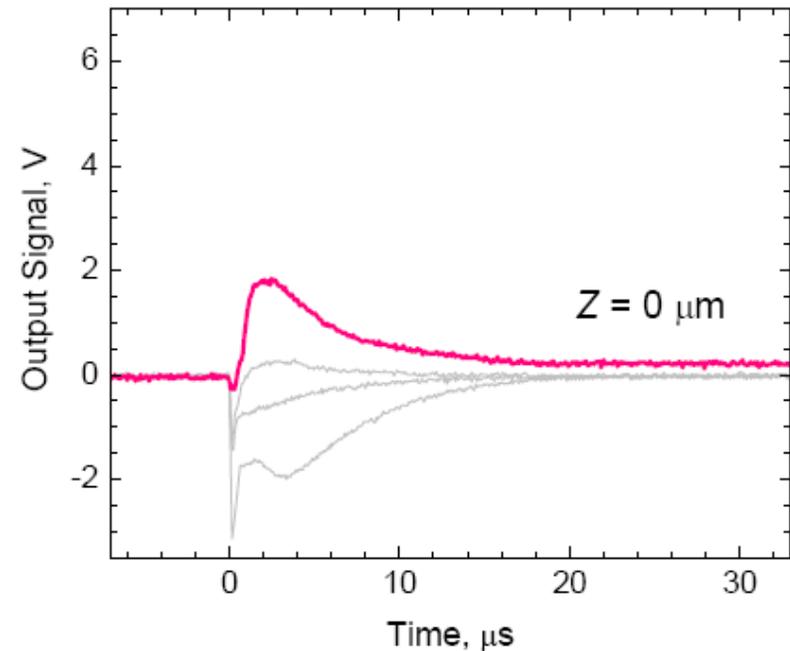
After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume



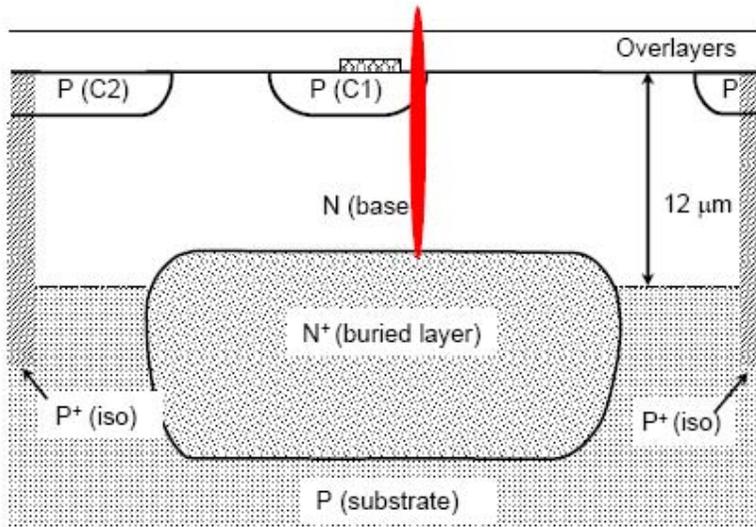
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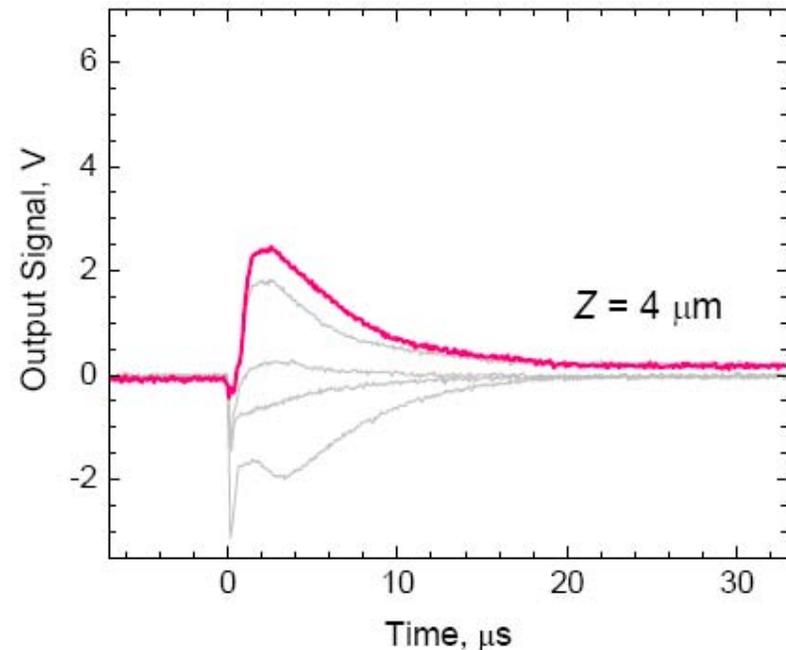
After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume



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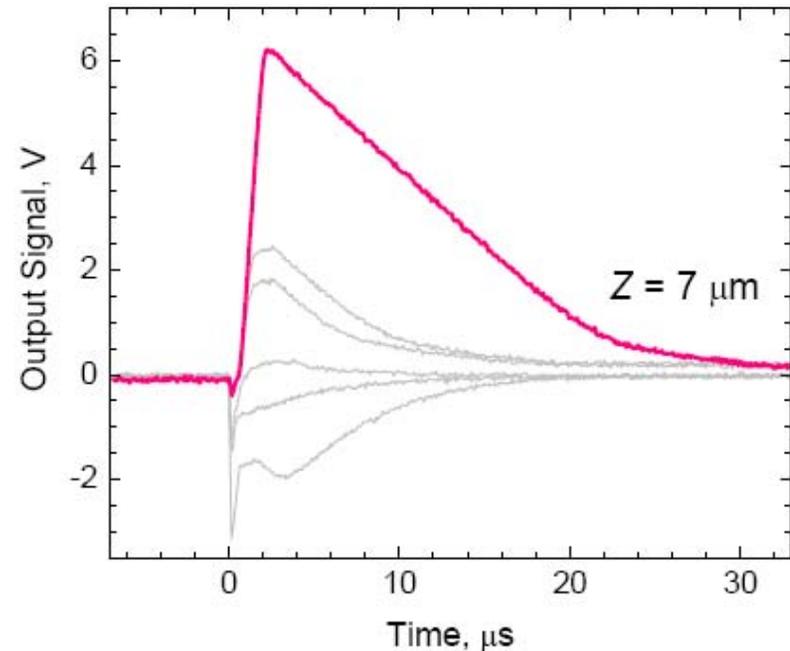
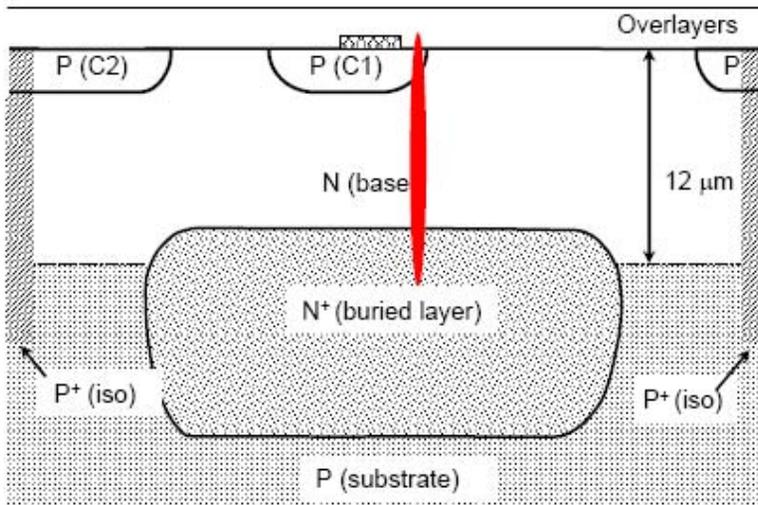


After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume

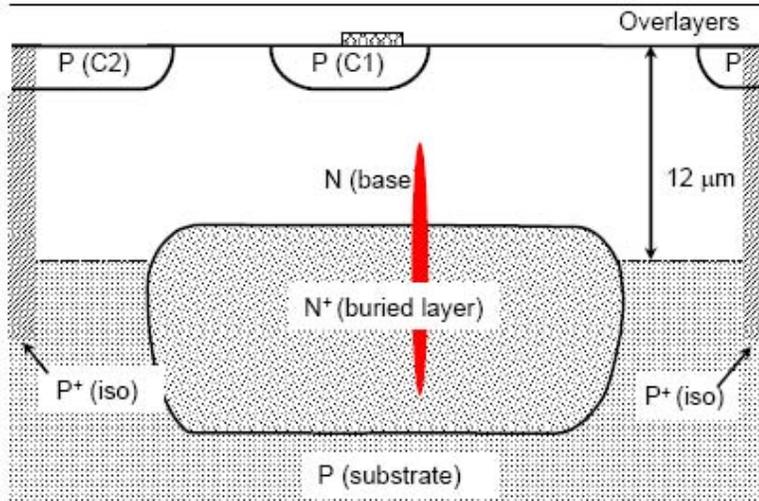
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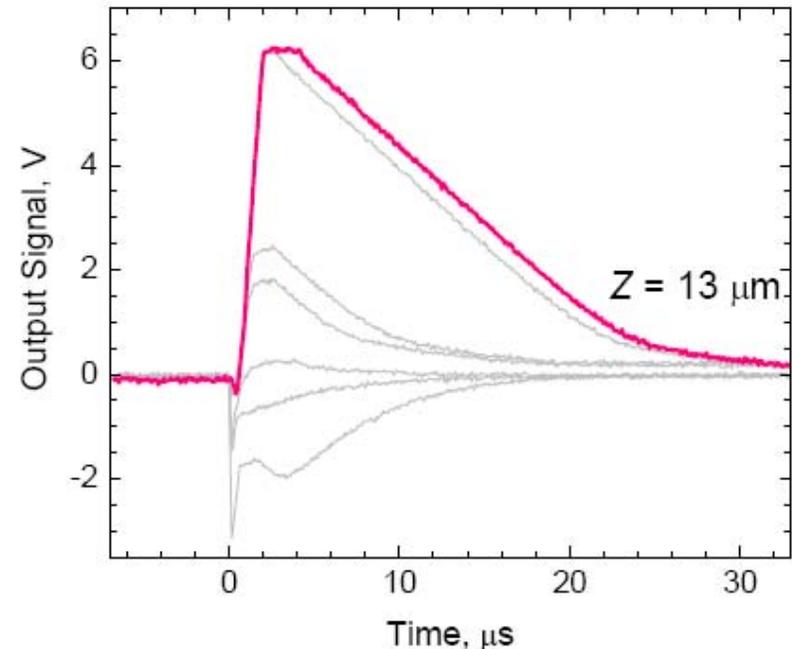
After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume



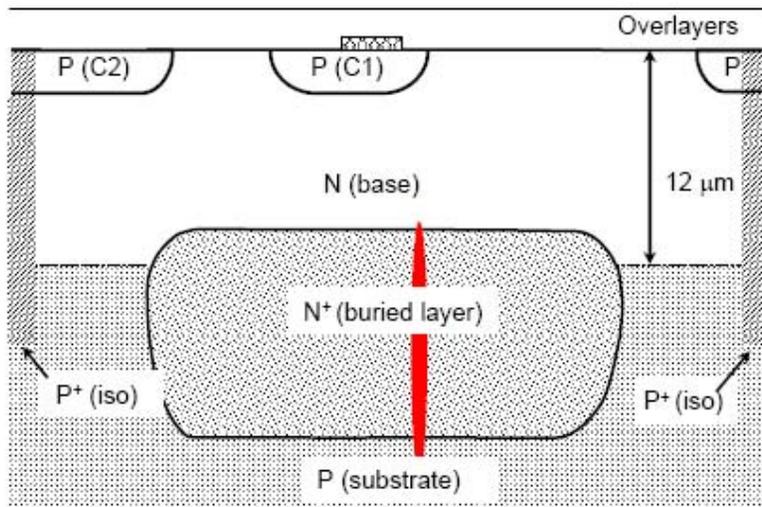
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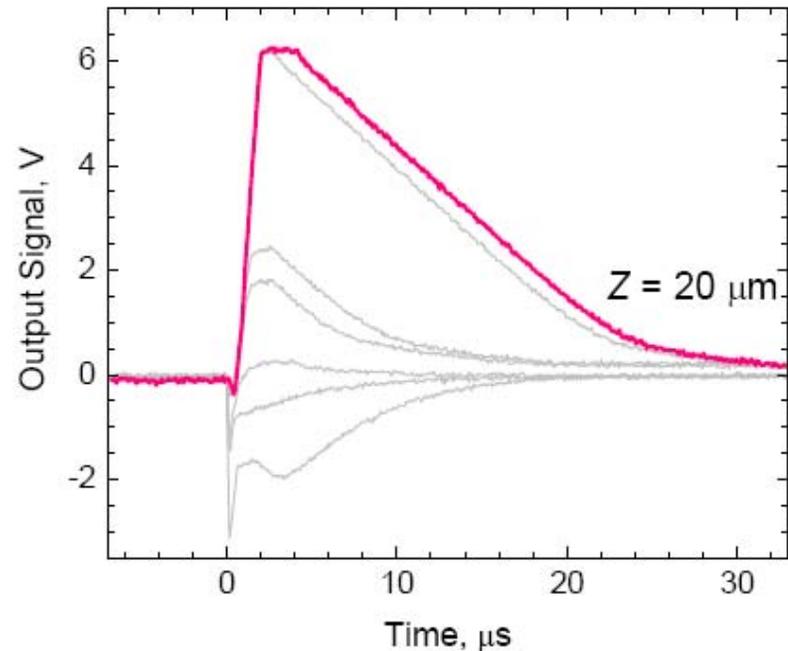
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SET event rate calculation in analog ICs

Thickness of sensitive volume



Inverting Configuration, gain of 20

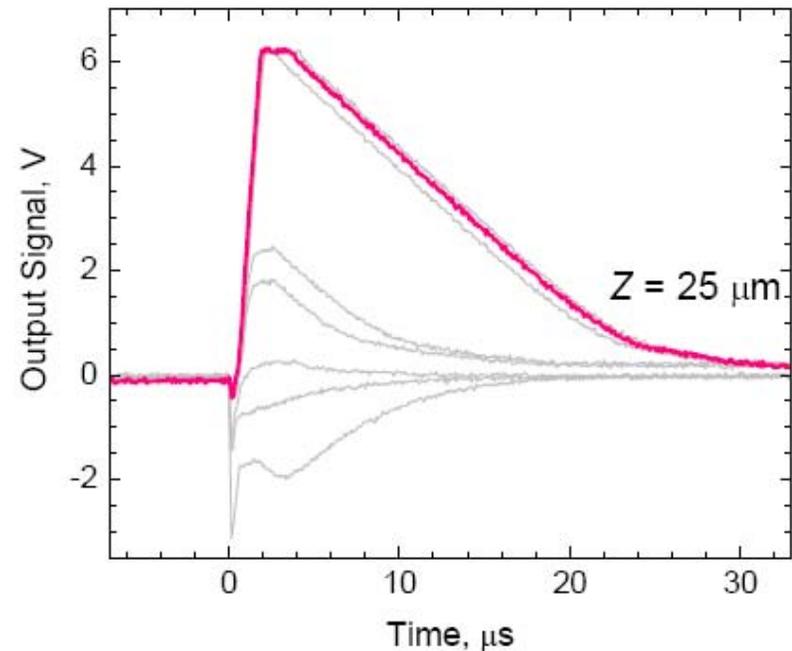
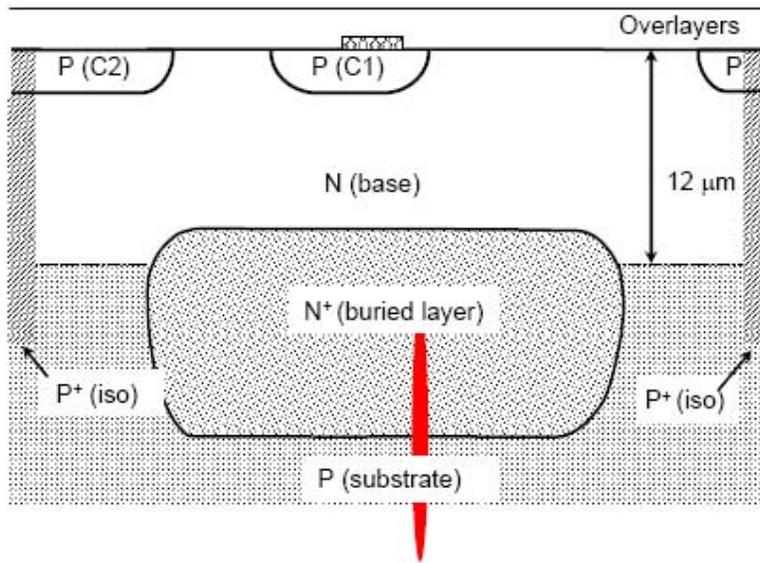


After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume

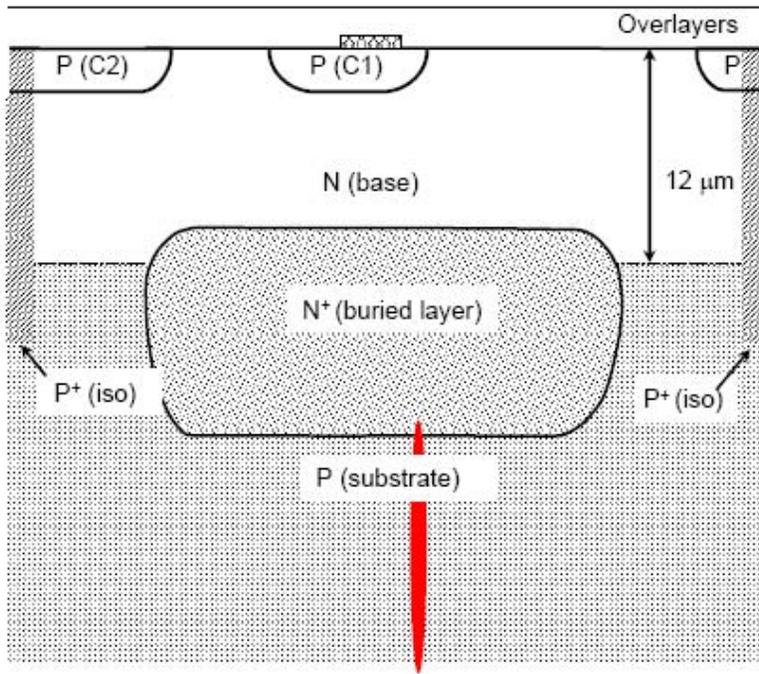
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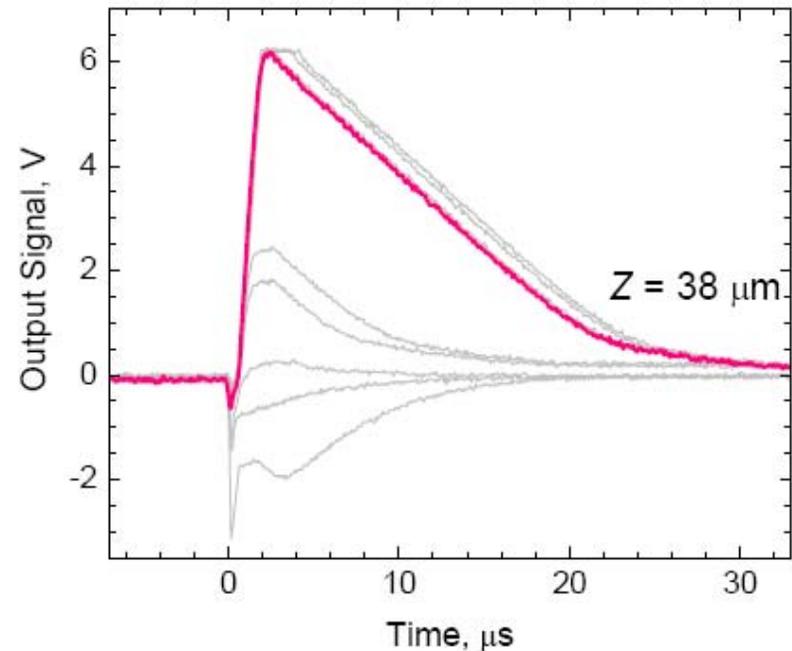
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SET event rate calculation in analog ICs

Thickness of sensitive volume



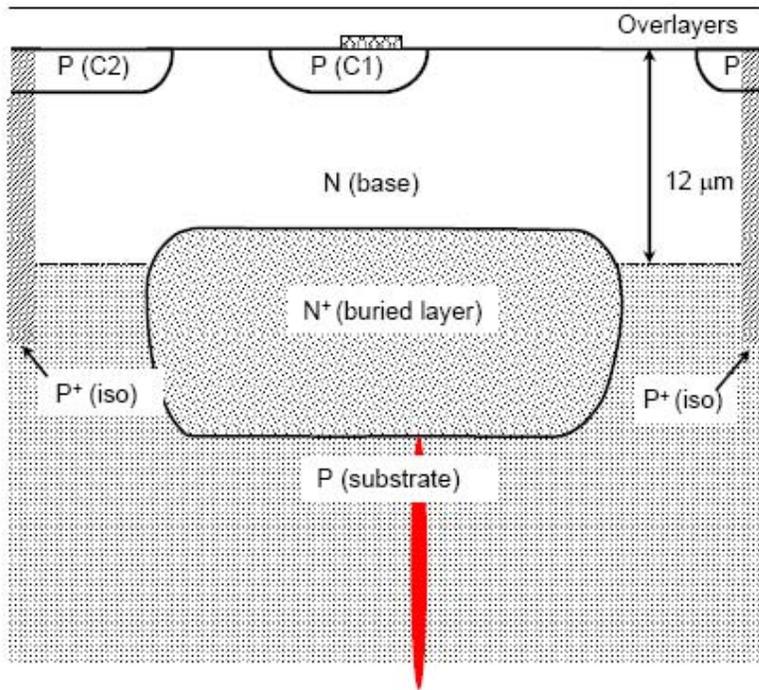
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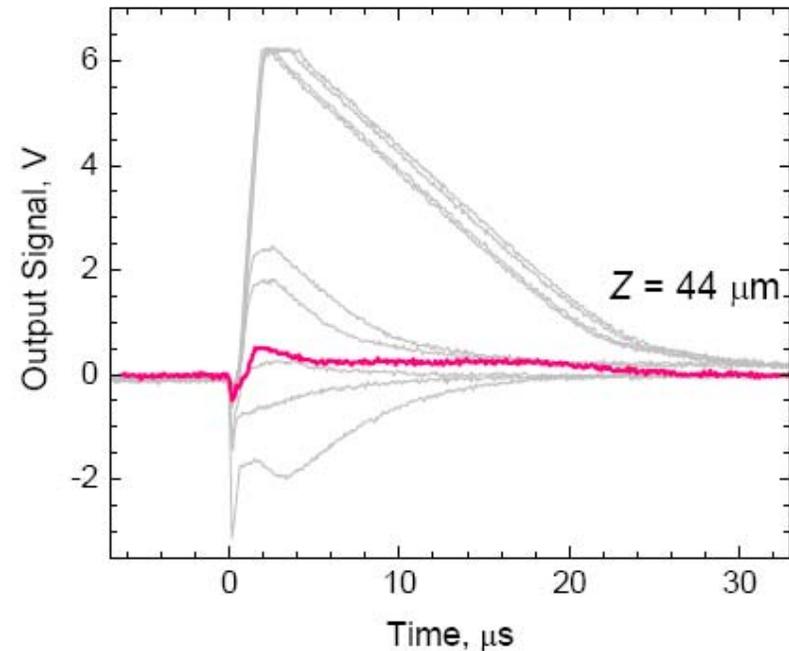
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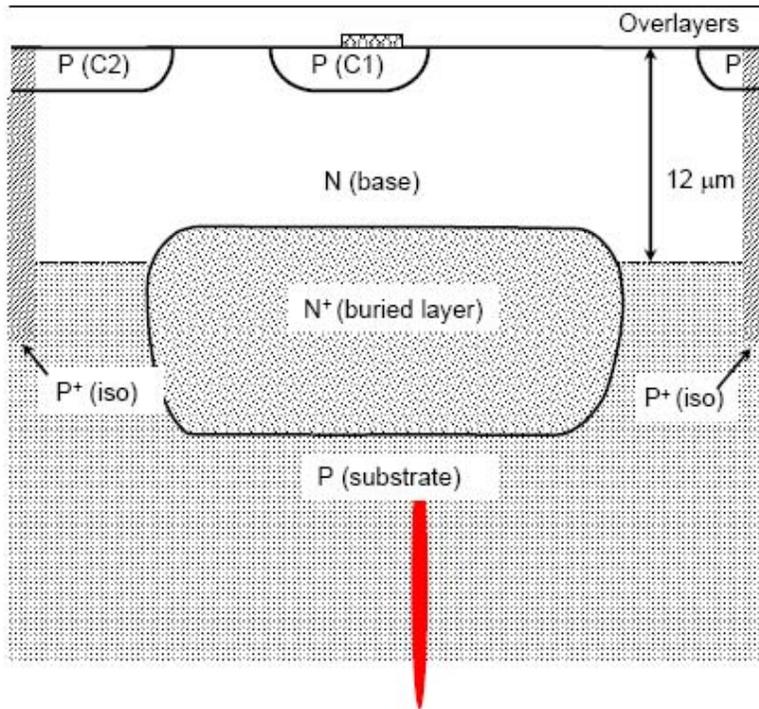
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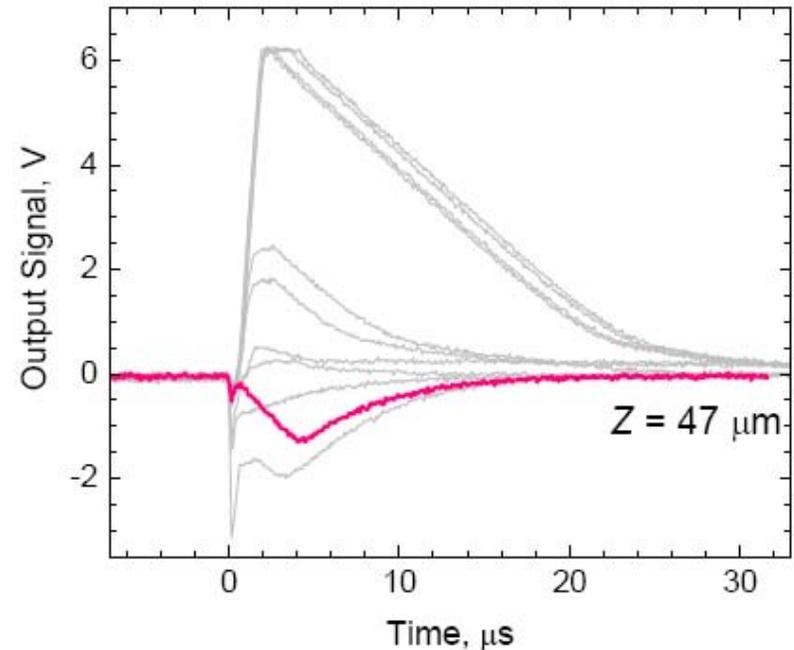
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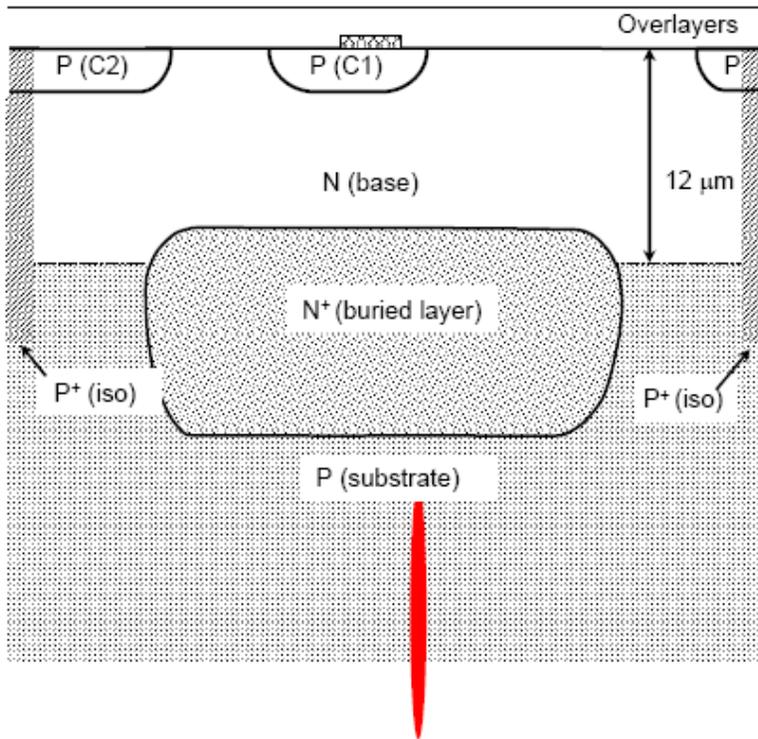
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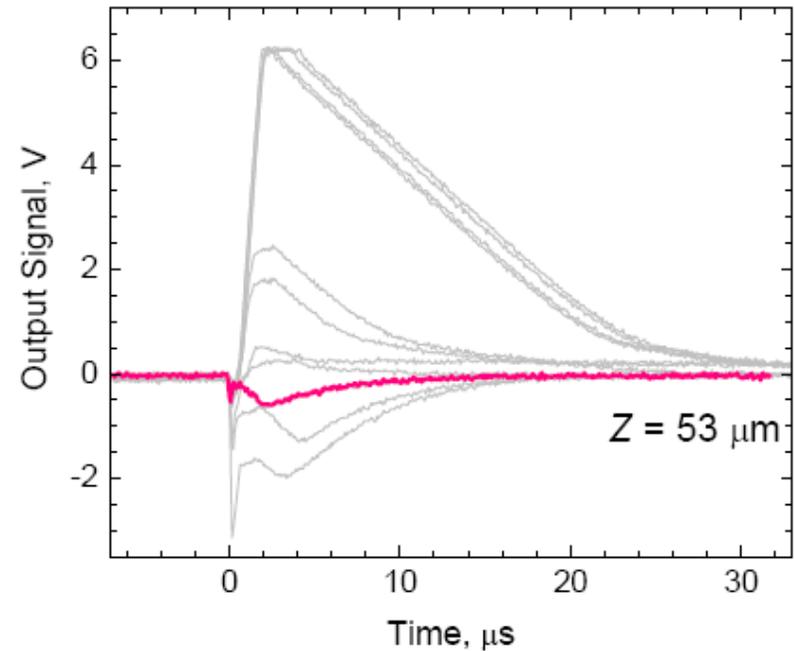
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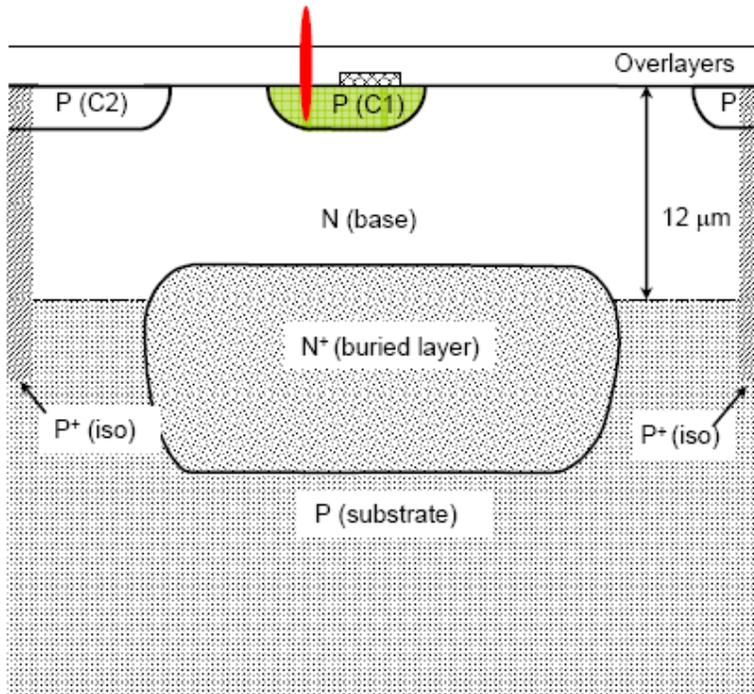
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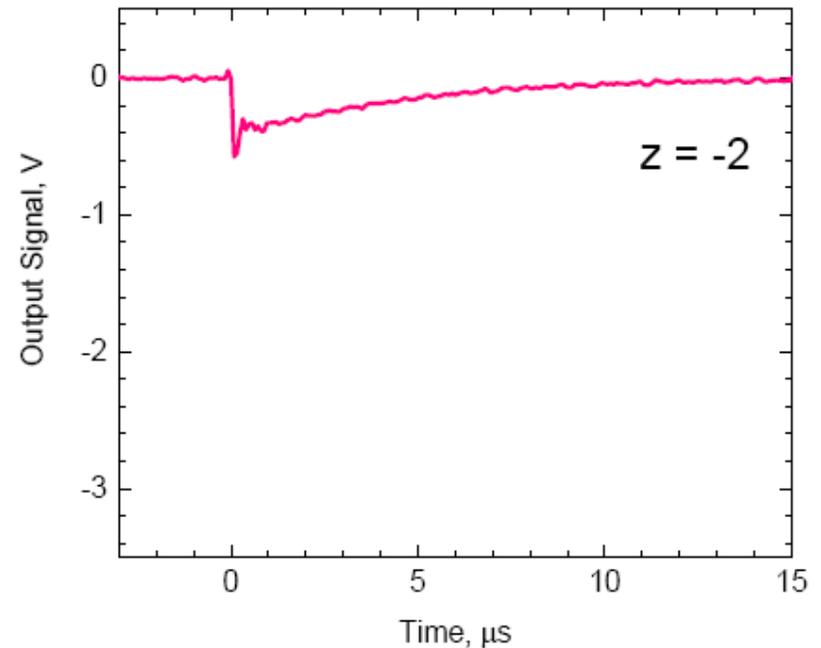
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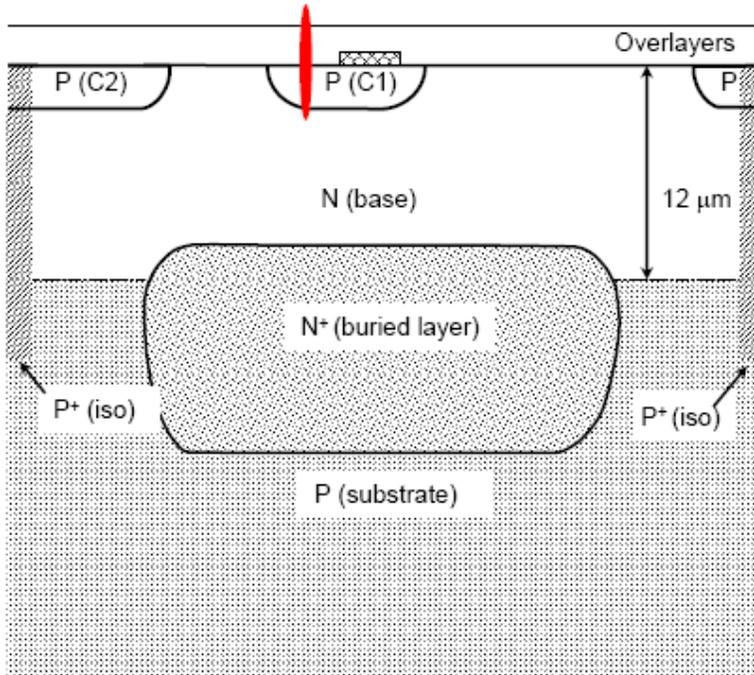
Low power measurements



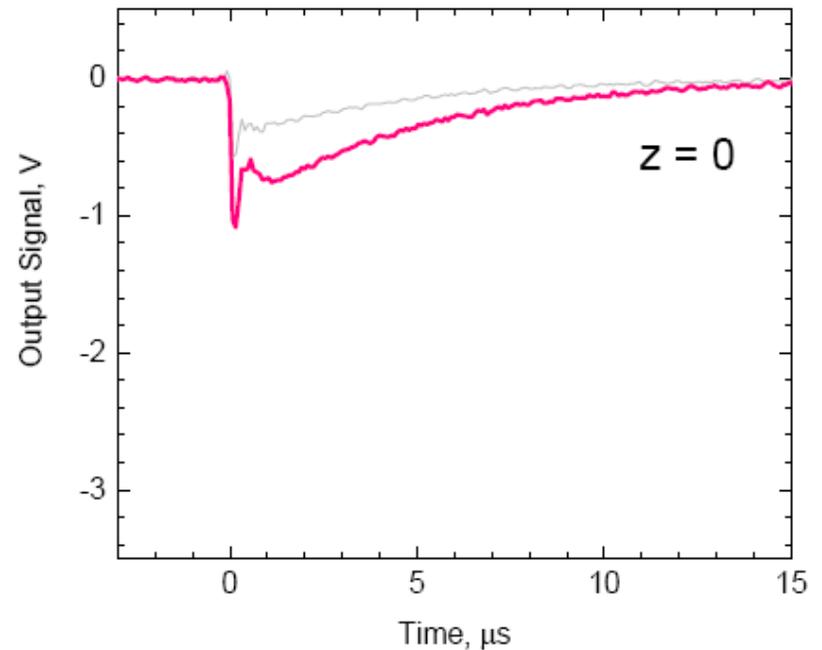
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SET event rate calculation in analog ICs

Thickness of sensitive volume



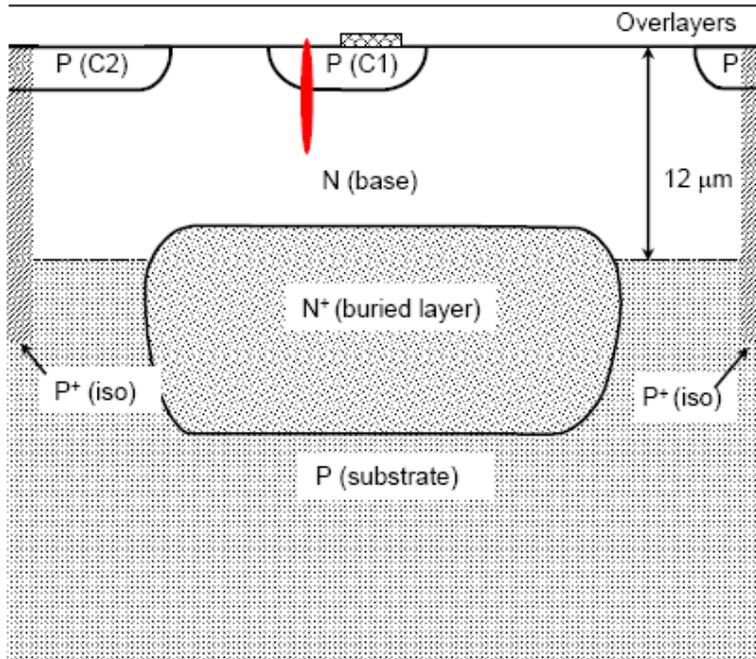
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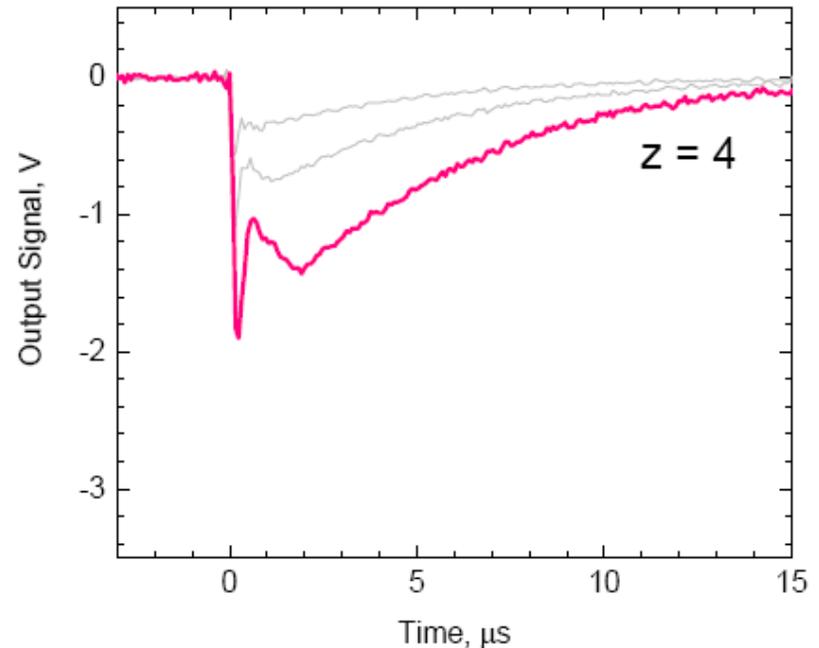
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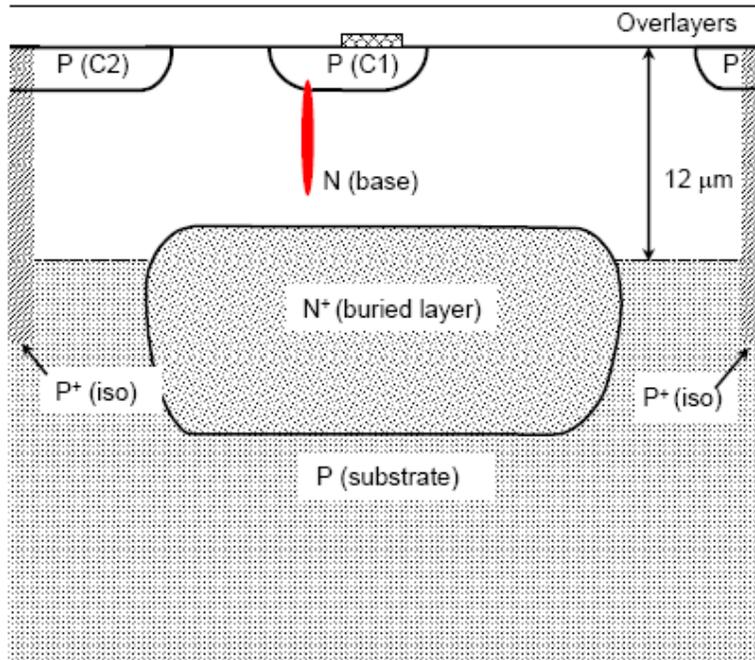
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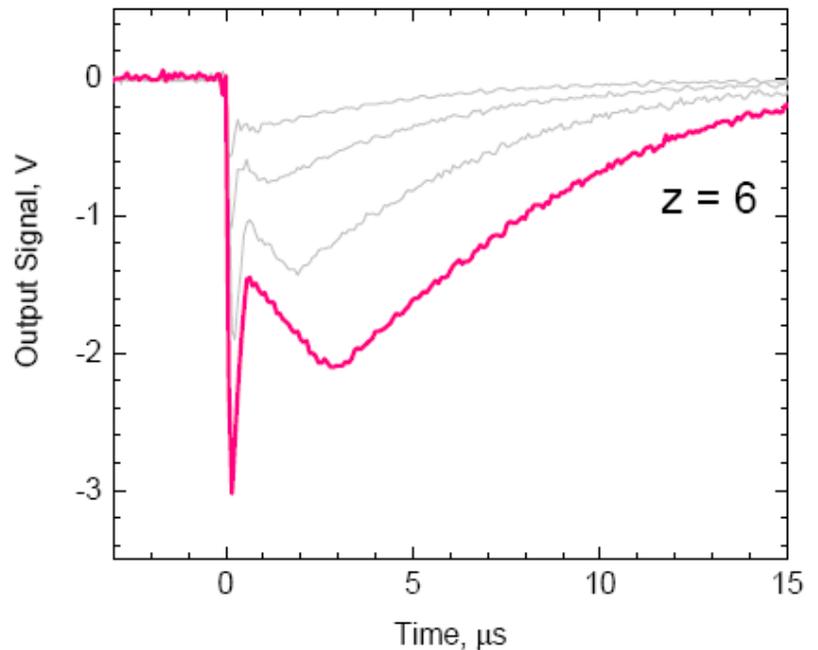
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SET event rate calculation in analog ICs

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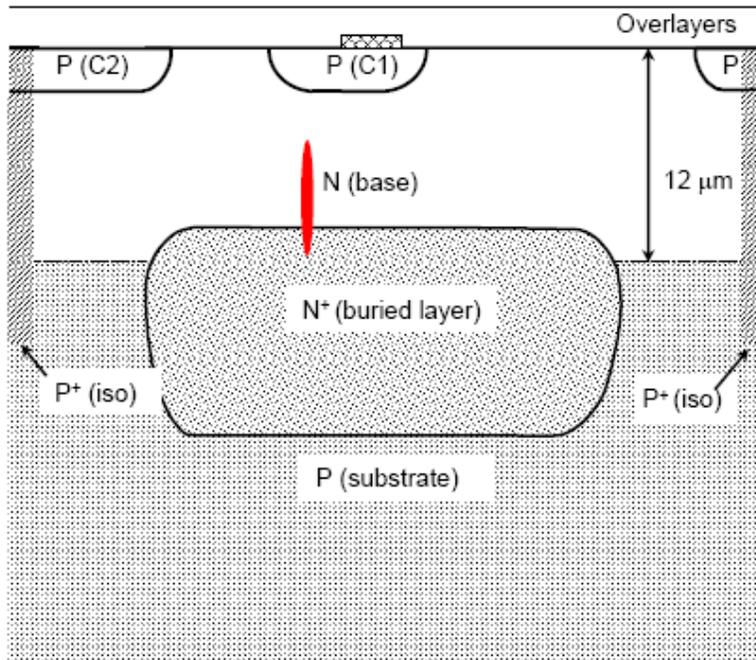
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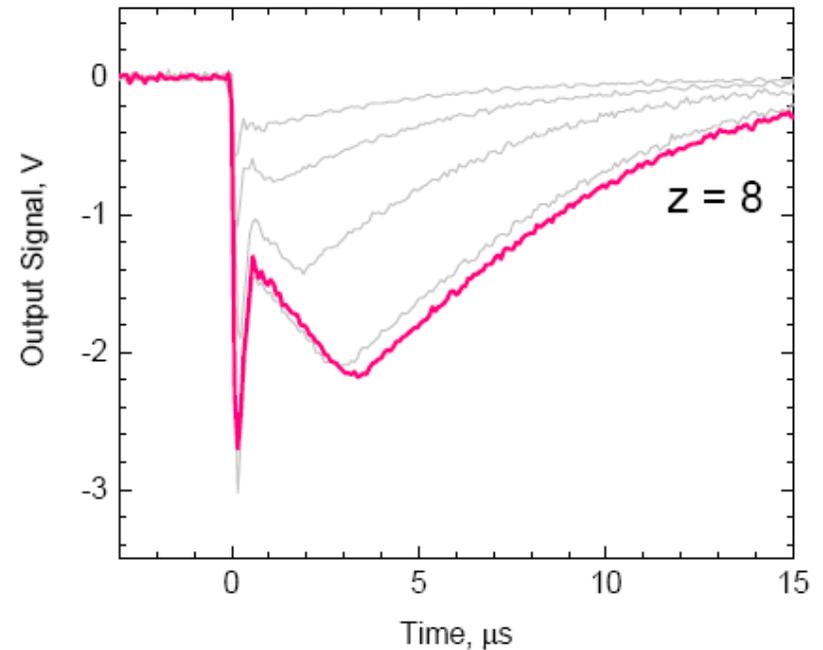
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SET event rate calculation in analog ICs

Thickness of sensitive volume



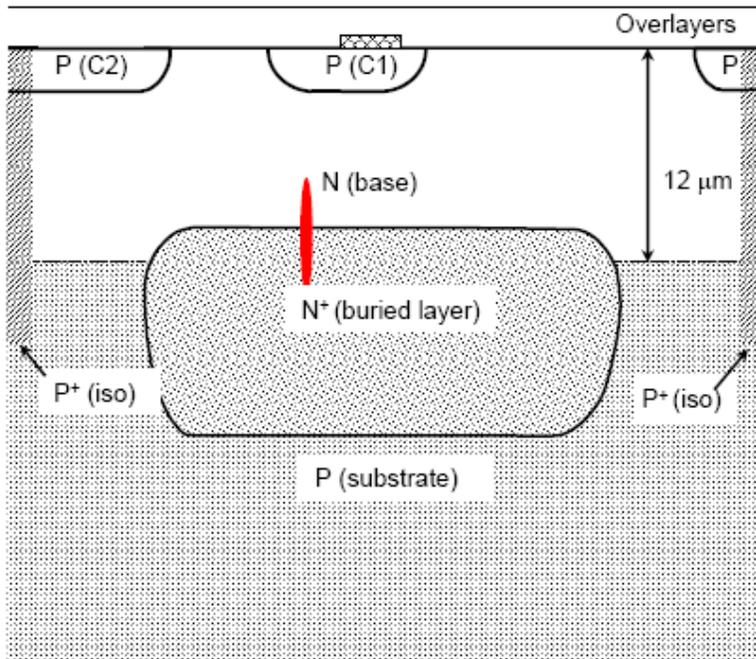
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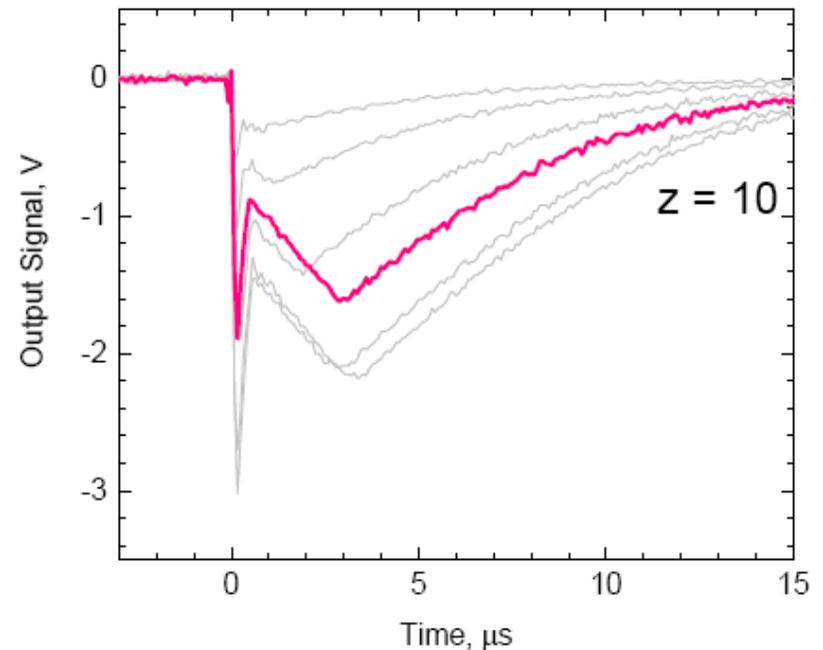
After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume



Low power measurements

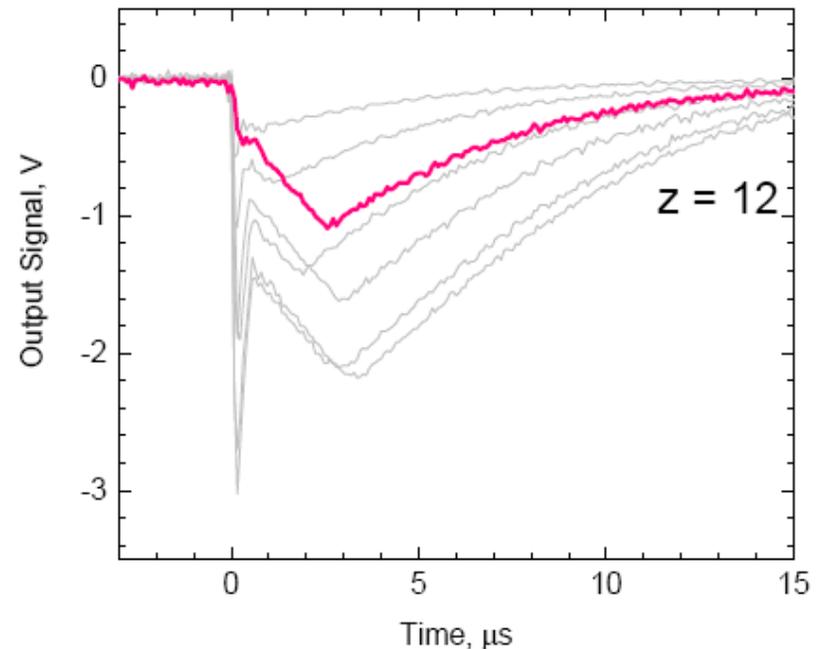
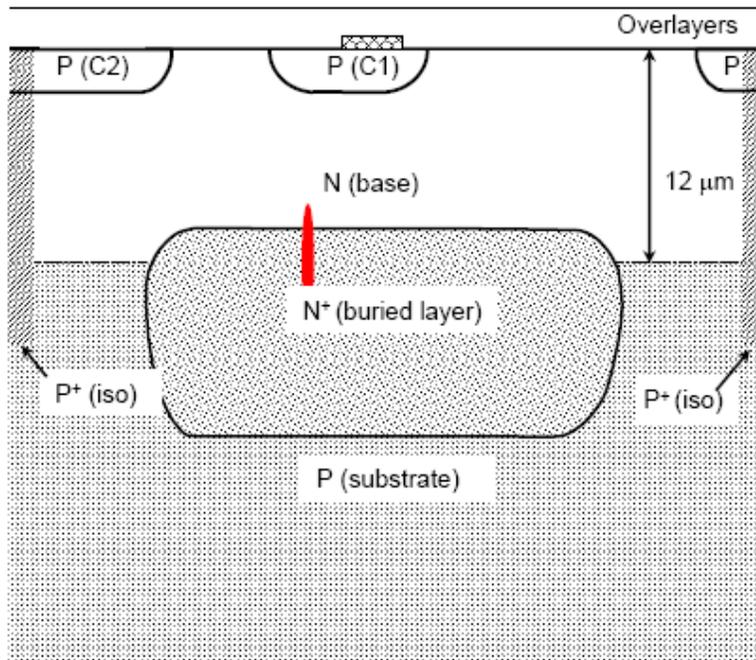


After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume

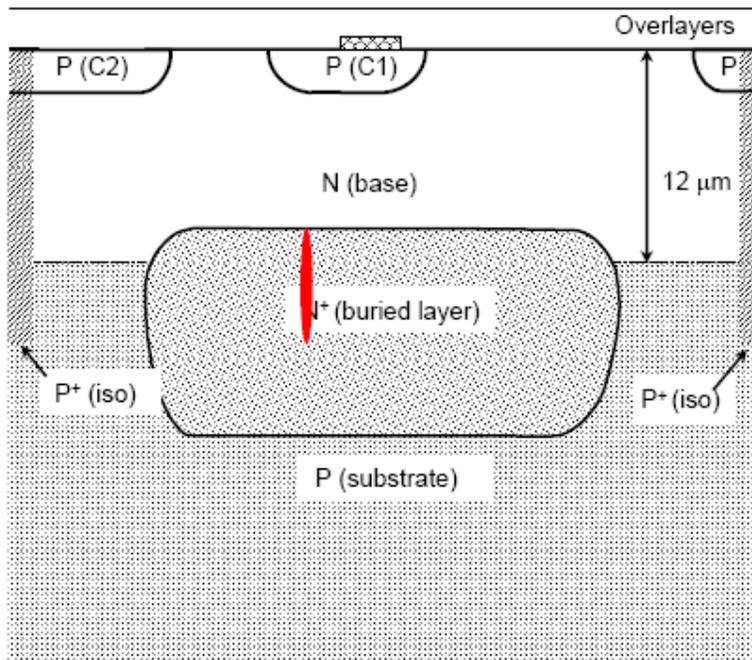
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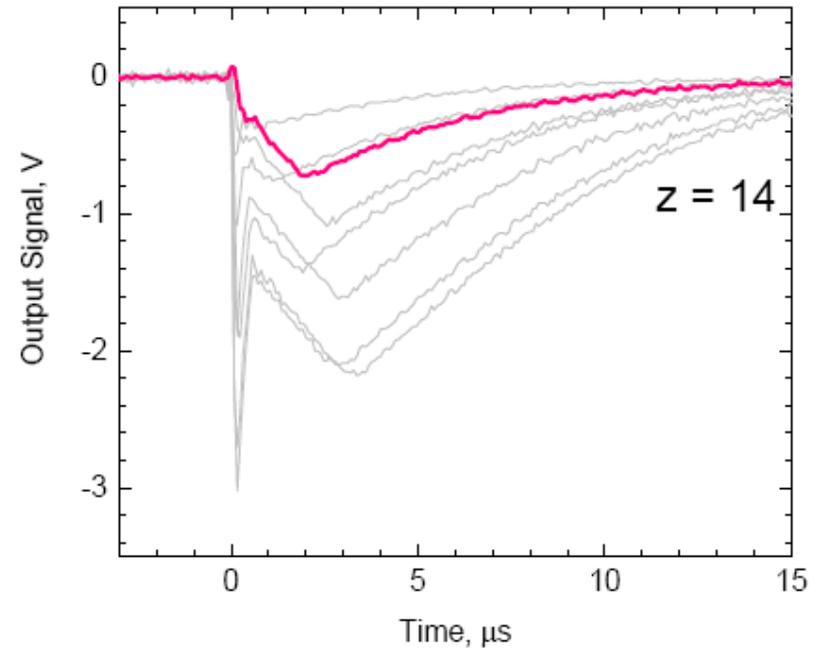
After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume



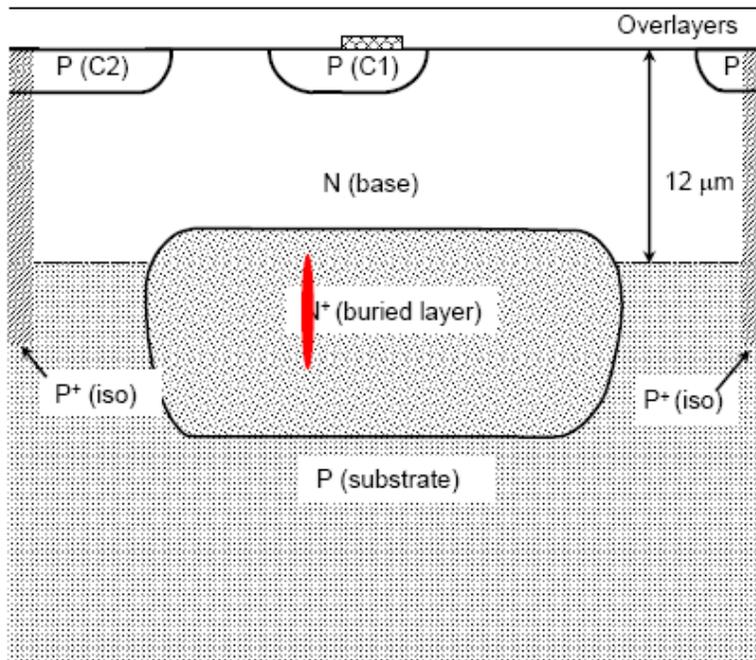
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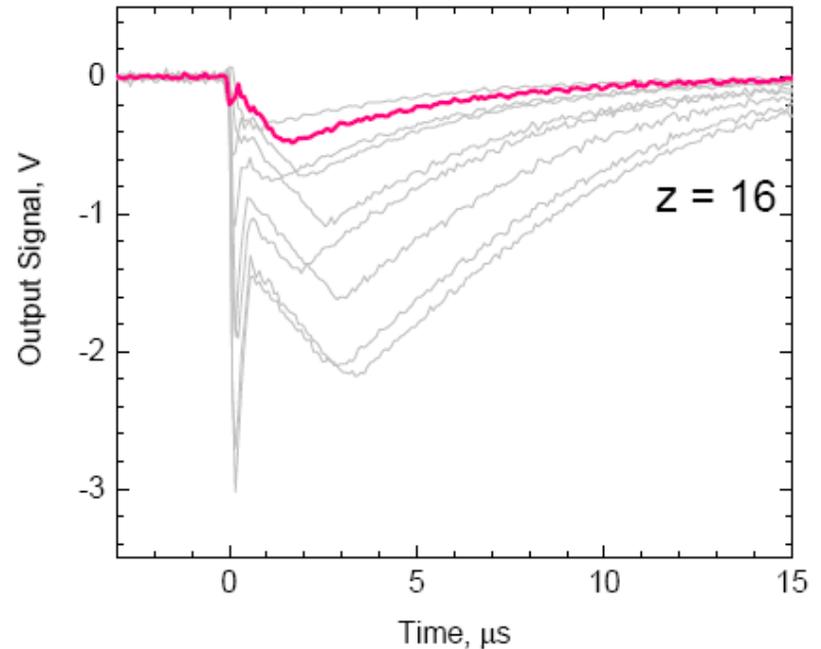
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SET event rate calculation in analog ICs

Thickness of sensitive volume



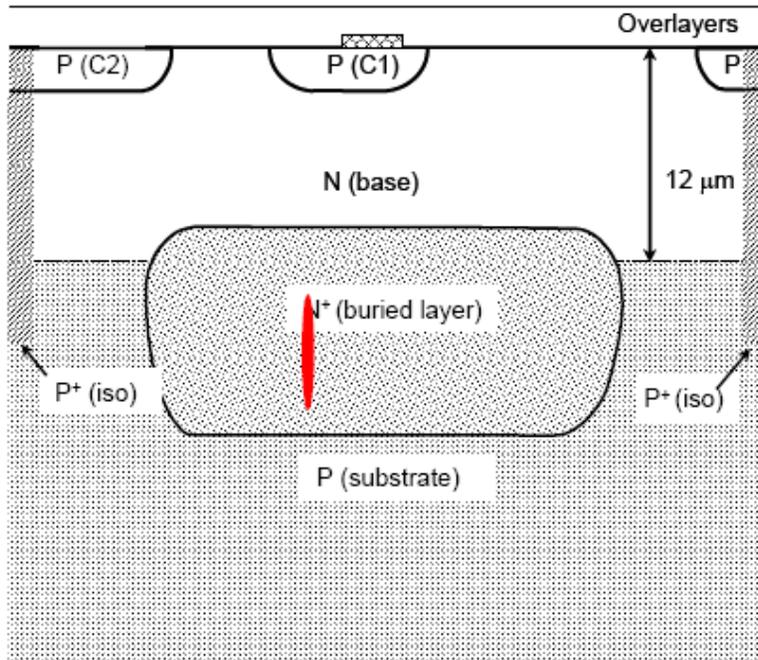
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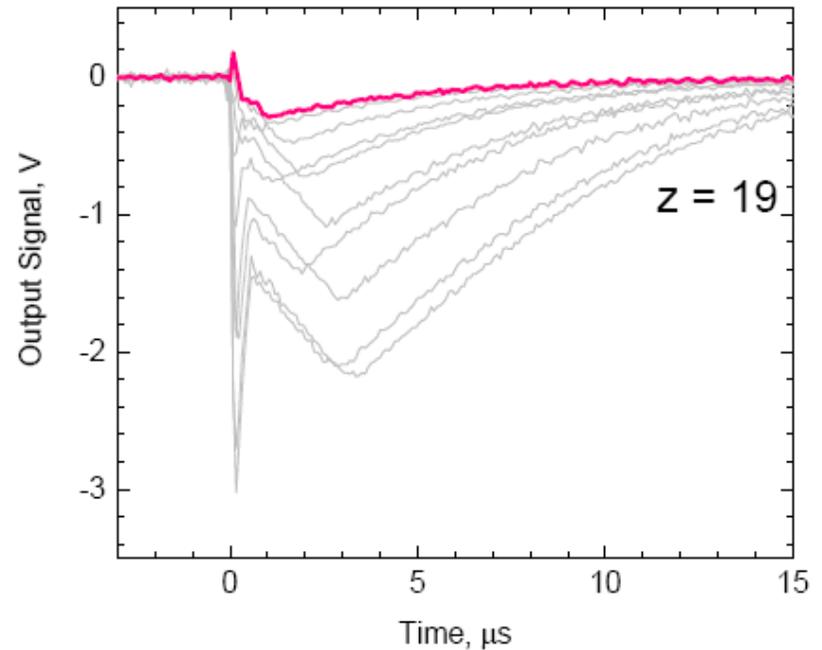
After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume



Low power measurements

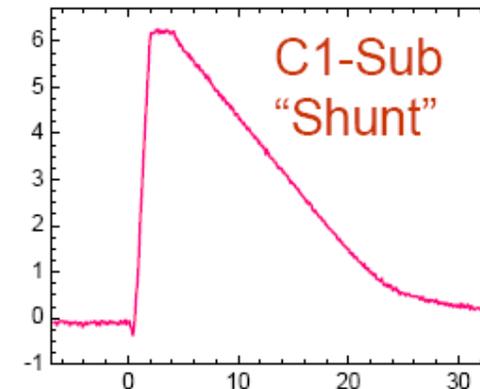
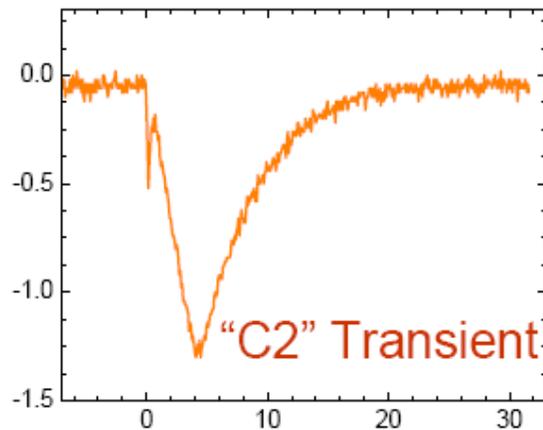
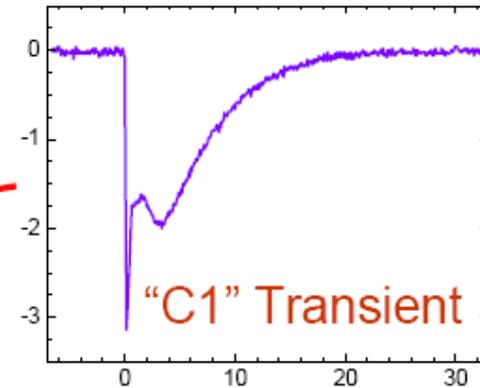
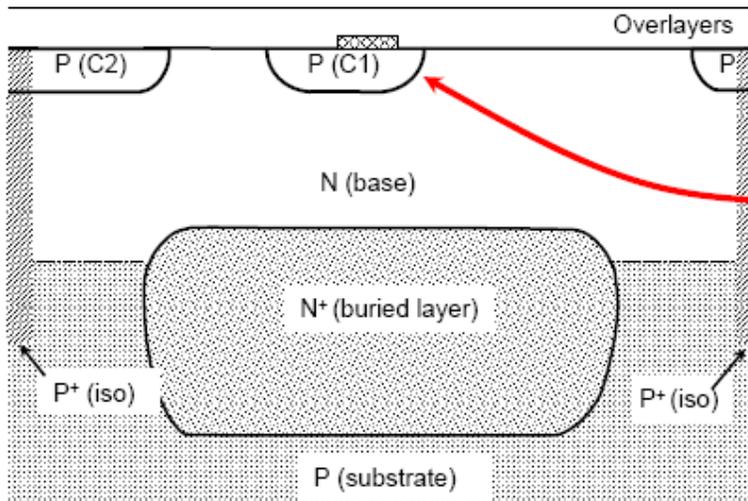


After McMorro, SERESSA 2006

SET event rate calculation in analog ICs

Thickness of sensitive volume

Z Dependence

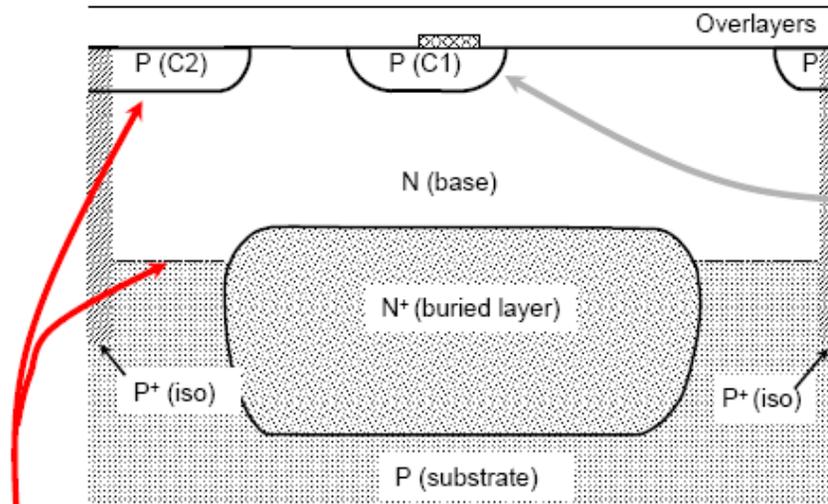


After McMorro, SERESSA 2006

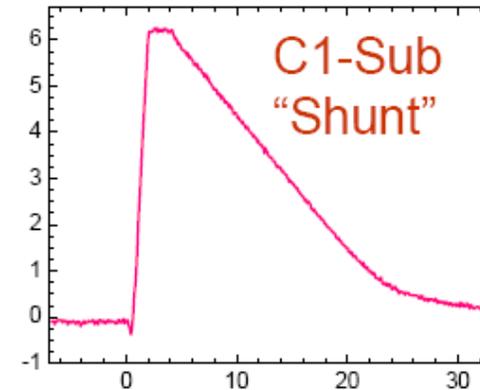
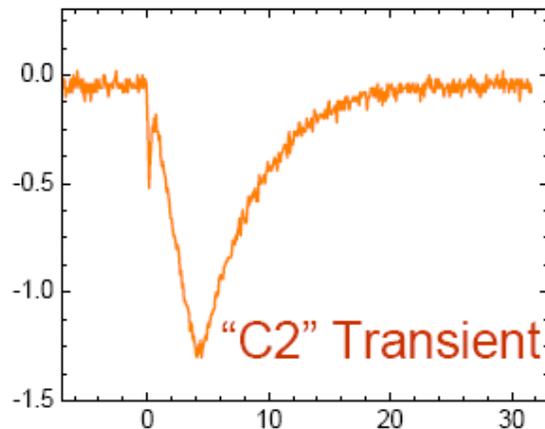
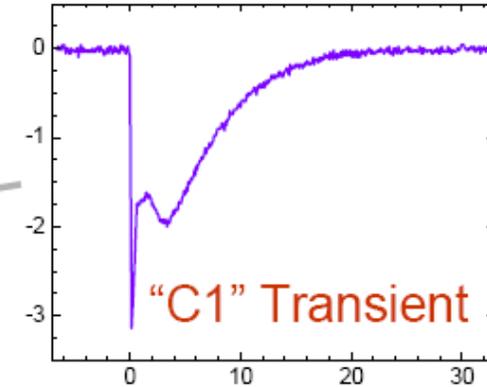
SET, 3rd RADECS Thematic Workshop
Villigen, Switzerland

SET event rate calculation in analog ICs

Thickness of sensitive volume



Z Dependence

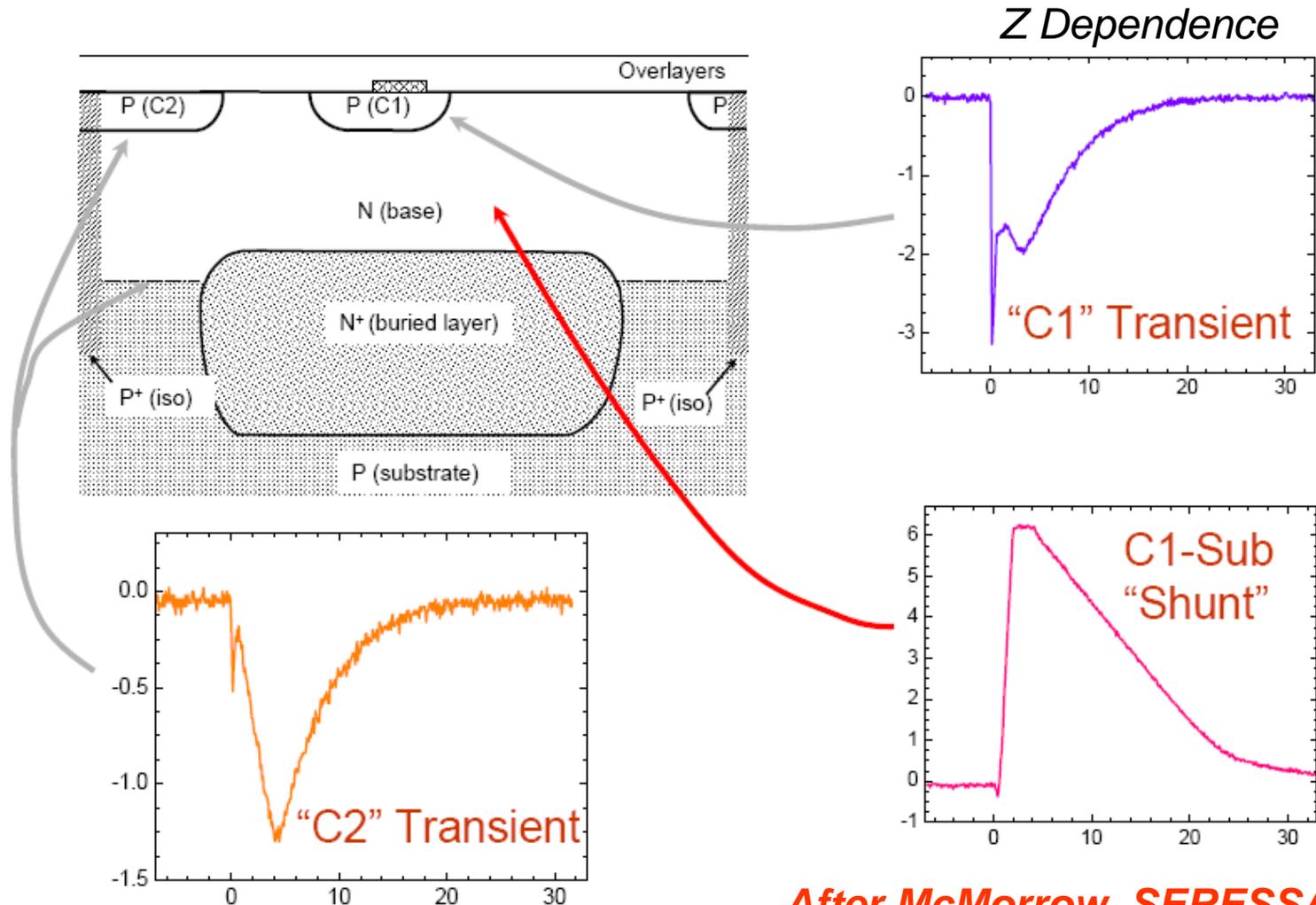


After McMorro, SERESSA 2006

SET, 3rd RADECS Thematic Workshop
Villigen, Switzerland

SET event rate calculation in analog ICs

Thickness of sensitive volume



After McMorro, SERESSA 2006

SET, 3rd RADECS Thematic Workshop
Villigen, Switzerland

SET event rate calculation

- Example, LM139
 - Effect of thickness of sensitive volume

Sensitive Volume Thickness (μm)	Rate of GCR induced SET (CREME96 solmin) #/comparator-day	Rate of SPE induced SET (CREME96 worst day) #/comparator-day
2	4.99E-03	1.63E+00
5	4.88E-03	9.4E-01
10	4.69E-03	5.1E-01
15	4.51E-03	3.2E-01
20	4.34E-03	2.1E-01
30	4.02E-03	1.3E-01
40	3.7E-03	1.2E-01
60	3.01E-03	9.83E-02

Flight data, SOHO

Module	Device	Observed in Flight (5 years)	Predicted
VIRGO	PM139	5	5
LASCO	UC1707	0	~0.1
ACU	UC1707	5	3

- *1 sensitive volume*
- *thickness = 2 μm*

From Harboe-Sorensen, RADECS 1999 & 2001 Proceedings

Flight data, MAP

- **Flight Data:**
 - One anomaly during November 5 solar event
 - One anomaly in 2 years
- **Predictions: PM139**

Sensitive volume thickness (μm)	GCR SET rate CREME 96 solmax (#/comparator-year)	Solar Event SET rate CREME 96, worst day (#/comparator-day)
10	6.57E-01	5.1E-01
15	6.21E-01	3.0E-01
20	5.84E-01	1.8E-01
30	5.48E-01	6.5E-02
40	4.75E-01	4.4E-02
60	3.61E-01	3.4E-02

After POIVEY, RADECS 2002

SET, 3rd RADECS Thematic Workshop
Villigen, Switzerland

Conclusion

- Most SET RHA issues are related with the bounding of part response.
- An accurate characterization allows an accurate analysis.
- Low confidence shall be given to SET rates predictions.
- Your comments are welcome.



Backup slides

Ronan Marec, et al
RADECS 2001

